

MAGNETIZATION DYNAMICS USING ULTRASHORT MAGNETIC FIELD PULSES

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Abstract

Very short and well shaped magnetic field pulses can be generated using ultra-relativistic electron bunches at Stanford Linear Accelerator. These fields of several Tesla with duration of several picoseconds are used to study the response of magnetic materials to a very short excitation. Precession of a magnetic moment by 90 degrees in a field of 1 Tesla takes about 10 picoseconds, so we explore the range of fast switching of the magnetization by precession.

Our experiments are in a region of magnetic excitation that is not yet accessible by other methods. The current table top experiments can generate fields longer than 100 ps and with strength of 0.1 Tesla only.

Two types of magnetic were used, magnetic recording media and model magnetic thin films. Information about the magnetization dynamics is extracted from the magnetic patterns generated by the magnetic field. The shape and size of these patterns are influenced by the dissipation of angular momentum involved in the switching process.

The high-density recording media, both in-plane and perpendicular type, shows a pattern which indicates a high spin momentum dissipation. The perpendicular magnetic recording media was exposed to multiple magnetic field pulses. We observed an extended transition region between switched and non-switched areas indicating a stochastic switching behavior that cannot be explained by thermal fluctuations.

The model films consist of very thin crystalline Fe films on GaAs. Even with

these model films we see an enhanced dissipation compared to ferromagnetic resonance studies. The magnetic patterns show that damping increases with time and it is not a constant as usually assumed in the equation describing the magnetization dynamics. The simulation using the theory of spin-wave scattering explains only half of the observed damping. An important feature of this theory is that the spin dissipation is time dependent and depends on the large angle between the magnetization and the magnetic field.

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Chapter 1

Introduction

If one wants to study magnetic phenomena at short time scales a method is to apply a very short pulse magnetic field and study the response to it. The peak amplitude of the magnetic field has to be high to obtain observable effects. The reason is that any magnetic moment precesses in the magnetic field, this is the main effect of a magnetic field on a magnetic moment, see figure 1.1. Since the precession speed is proportional to the magnetic field intensity ($\omega = \gamma \mathbf{B}$), in order to have reasonable precession angles in very short time, one needs a big magnetic field.

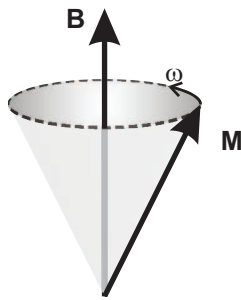


Figure 1.1: The precession around the magnetic field direction is the most important effect of a magnetic field on a magnetic moment.

It is difficult to make very short magnetic field pulses with conventional solid-state techniques when the electric current used in generating the magnetic field has

to overcome inevitable capacitive and inductive effects. However, if one makes an electric current with relativistic electrons in vacuum, those effects are much more reduced. A short current pulse can be made more easily because the relativistic electrons can be packed more efficiently (relativistic contraction). The drawback is one has to use an accelerator but this method can produce pulses on the order of tens of femtoseconds, with the required high intensity of the magnetic field.

This thesis explores the precessional switching in magnetic recording media and model magnetic thin films using the magnetic field associated with the electron bunch of the Stanford Linear Accelerator. The perpendicular magnetic media samples show there is an additional random mechanism beside the thermal fluctuations that affects the switching. All magnetic samples present enhanced damping, only part of which could be explained by spin wave scattering of the uniform mode using micromagnetics simulation.

After presenting the characteristics of the magnetic field of the electron bunches we show the experimental setup and the imaging methods used for viewing the magnetic patterns. Then the equation governing the magnetization dynamics is introduced and the main results of the experiments follow. Appendices contain supporting information and related new ideas triggered by thinking about the experiments.

Chapter 2

Electromagnetic Effects of an Electron Pulse

In this chapter we will calculate the electromagnetic field of an ultra-relativistic electron beam and understand what are some of the effects of these fields on different materials. Since the electron beam is very short we have to look at the relevant time and length scales and how they arise in Maxwell's equations.

2.1 Why relativistic electron beam?

Very energetic electron beams can be produced at high energy physics facilities, like linear accelerators. Typically they are used to probe the matter at ultra small time and length scales in particle collisions. However one can also use the electromagnetic field associated with the electron beam to do condensed matter physics because, being long range, the electric and magnetic field extend far enough (hundreds of microns) to be useful.

As an example, the Stanford Linear Accelerator facility can deliver an electron pulse with the energy around 28 GeV. The pulse normally has a gaussian shape in

all 3 directions, for example in one experiment we had the longitudinal $\sigma_z = 700\mu m$ and transversal $\sigma_x = 5\mu m$ and $\sigma_y = 3\mu m$. The number of electrons in the beam is around $n_e = 10^{10}$ electrons. For this energy the relativistic factor $\gamma = 1/\sqrt{1 - \beta^2} \approx 5.5 \times 10^4$, $\beta = v/c$, v being the electron velocity.

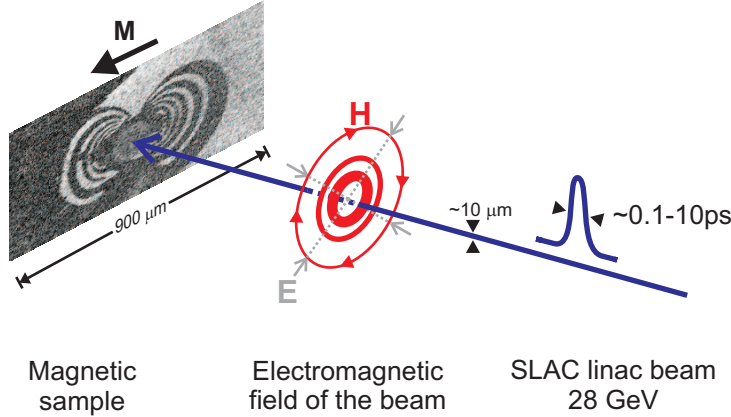


Figure 2.1: A typical experimental setup for magnetic thin film samples, shown here with an initially in-plane magnetized sample. The electric and magnetic fields associated with the electron bunch influence the sample's magnetic and electric state. The effect of the magnetic field after one pulse has gone through is a magnetic pattern.

An illustration of how this electromagnetic field can be used is shown in figure 2.1, where we shoot electrons through a thin film sample. As the electron beam passes through the sample it damages an area roughly twice the section of the beam. The small amount of heat generated in that small area can only propagate with the phonon speed, on the order of the sound speed, which is slow compared to magnetic processes of interest to us. Since the damage is localized there is a chance to observe at larger distances the effects of the electric and magnetic fields associated with the pulse. Hence the requirement to have a well focused beam.

The small spatial extent of the electron beam is possible because the electromagnetic force between electrons is reduced as their velocity approach that of light. To see how this comes about we consider two electrons moving with the same velocity $\mathbf{v}$

in the same direction. The force exerted by one electron on another is given by the Lorentz formula

$$\mathbf{F} = e(\mathbf{E} + \mathbf{v} \times \mathbf{B}) \quad (2.1)$$

where $\mathbf{E}$, $\mathbf{B}$ are the electric and magnetic field generated by one electron at the location of the other, e being the electric charge of the electron.

It turns out that the force can be expressed as gradient of a potential, called the convective potential (see appendix A.1).

$$\mathbf{F} = -\nabla\psi, \quad \text{where} \quad \psi = \frac{e^2(1 - v^2/c^2)}{4\pi\epsilon_0 s} \quad (2.2)$$

with $s = r\sqrt{1 - v^2/c^2 \sin^2 \theta}$ defined in A.8, r being the distance between electrons and θ the angle r makes with v . As an application, the figure 2.2 illustrates how the measured force between electrons is modified when the electrons move. The force

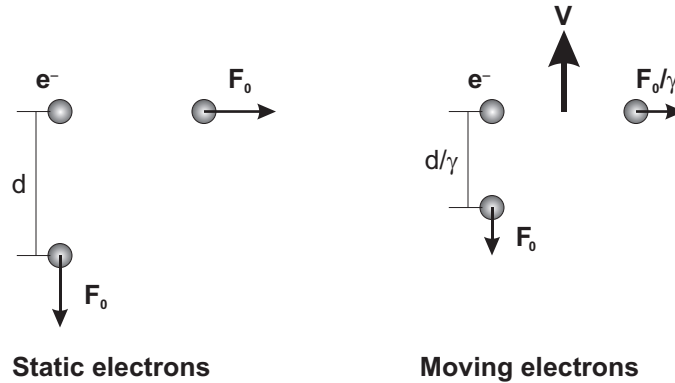


Figure 2.2: Comparison of forces acting between static electrons and moving electrons of an electron bunch. In a direction parallel with the velocity the electromagnetic force remains unchanged; notice that the distance between electrons is reduced by relativistic contraction. Perpendicular to the velocity direction, the distance measured in the lab frame doesn't change although the force, due to both electric and magnetic field, is reduced. The reason is that the magnetic Lorentz force acts in the opposite sense to the electric force. (The two parallel running electrons are similar to two parallel electric currents that attract each other and two parallel charged lines that repel each other.)

between moving electrons in the lab frame decreases as $1/\gamma$ in transversal direction [?]. The repulsion between electrons (space charge effect) is then reduced, making possible a better focusing. Moreover, the relativistic contraction makes the pulse look shorter in the longitudinal direction in the lab frame.

2.2 Electromagnetic fields of an electron beam

Because space and time are so closely related in the relativistic regime a fast moving electron, i.e. with high velocity = space/time, has significantly different electromagnetic field than a static electron.

The electric field of an electron seen in the lab frame are plotted below for different values of $\beta = v/c$ in a polar plot of the intensity with respect to the angle θ made by the field with the velocity direction (figure 2.3).

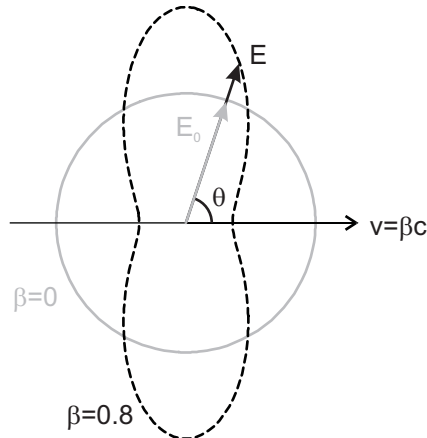


Figure 2.3: Polar plot of angular dependence of the electric field intensity for a relativistic electron (E_0 is the electric field of a static electron). The electric field as measured in the lab frame is enhanced in the perpendicular direction to the motion and reduced in the parallel direction.

The formula describing the electric field is [?]

$$\mathbf{E}(\mathbf{r}) = \frac{e\hat{\mathbf{r}}}{4\pi\epsilon_0 r^2} \frac{1 - \beta^2}{(1 - \beta^2 \sin^2 \theta)^{3/2}} \quad (2.3)$$

where r is the distance between present position of the electron and the point of observation. The electric field is radial, but it is isotropic only for $\beta = 0$. Along the direction of motion ($\theta = 0, \pi$), the field strength is smaller by a factor of γ^{-2} , while in transverse directions ($\theta = \pi/2$) it is larger by a factor of γ .

The moving electron is equivalent to an electric current, so it creates also a magnetic field given by

$$\mathbf{B}(\mathbf{r}) = \frac{\boldsymbol{\beta} \times \mathbf{E}}{c} \quad (2.4)$$

An artistic view of the direction of the electric and magnetic fields is illustrated in figure 2.4.

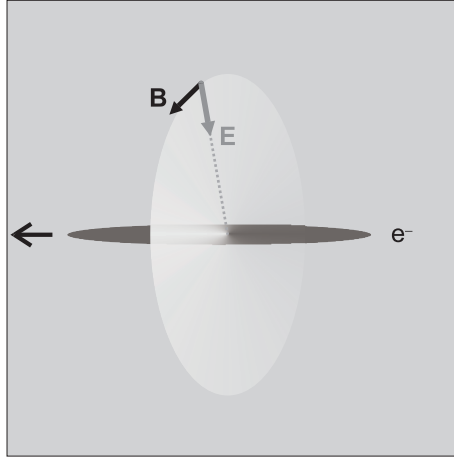


Figure 2.4: Electromagnetic fields are significant only in a plane perpendicular to the direction of propagation.

As the speed approaches the speed of light the electric field is concentrated in a thin disk perpendicular to the direction of motion with an angular spread of $2/\gamma$. In

the ultra-relativistic limit $v \sim c$, the thickness of the disk $2r/\gamma$ is very small and we can approximate it using the Dirac delta function $2r/\gamma \rightarrow 1/\delta(x - ct)$, x being the component of the position vector of the electron parallel with its velocity. We can then use the Gauss law with a very thin box to find the electric field close to the electron

$$\oint \mathbf{E} d\mathbf{S} = \frac{q}{\epsilon_0} \Rightarrow \mathbf{E}_\perp = \frac{q}{2\pi\epsilon_0 r} \delta(x - ct) \quad (2.5)$$

The formula for the electric field of an ultra-relativistic electron beam is just a

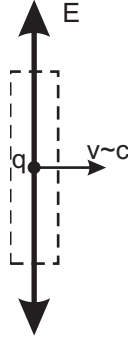


Figure 2.5: As the electric field is very much confined in a disc perpendicular to the velocity one can use the Gauss law in calculating the electric field of an ultra-relativistic electron. Here we enclose the charge with a thin cylindrical box. Only the side surface with area $2\pi r \, 1/\delta(x - ct)$ contributes to the total surface integral.

summation (convolution) of 2.5 over all the electrons. If the bunch has a charge linear density $\lambda(x)$ the electric field is

$$E_\perp = \frac{\lambda(x - ct)}{2\pi\epsilon_0 r} \quad (2.6)$$

Although in the actual beam the charge distribution is discrete and the random position of one electron inside the electron bunch follows a gaussian distribution the electromagnetic field becomes smooth very quickly farther away from the bunch center. As an illustration, figure 2.6 shows the potential from a uniform random distribution of 10^4 static electrons inside a line with length $100\mu m$ and cross section

$10\mu m \times 10\mu m$. As long as we are not interested in the effects very close to the beam

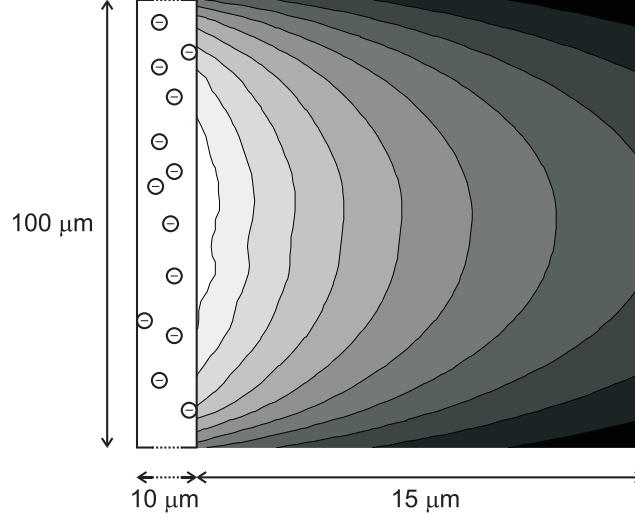


Figure 2.6: Equipotential lines of electric field for 10^4 electrons uniformly distributed in a long rectangular line. Note that the vertical dimension is scaled down, so the variations in that direction are enhanced. Even so, the potential lines look rather smooth and for almost all purposes the random discrete distribution can be replaced by a continuous average charge distribution.

we can neglect the randomness in the position of the electrons as only the average counts in the long range.

In general a charge has both velocity and acceleration and different types of electromagnetic fields are associated with them. A charge moving with velocity $\mathbf{v} = \boldsymbol{\beta}c$ and acceleration $\mathbf{a} = d\boldsymbol{\beta}/dt c$ will have magnetic and electric fields that are described, at some point $\mathbf{r} = r\mathbf{n}$ (see figure 2.7), by the following Liénard-Wiechert formula [?].

$$\begin{aligned} \mathbf{E}(\mathbf{r}, t) &= \frac{q}{4\pi\epsilon_0} \left[\frac{\mathbf{n} - \boldsymbol{\beta}}{\gamma^2(1 - \boldsymbol{\beta} \cdot \mathbf{n})^3 r^2} + \frac{\mathbf{n} \times (\mathbf{n} - \boldsymbol{\beta}) \times \dot{\boldsymbol{\beta}}}{c(1 - \boldsymbol{\beta} \cdot \mathbf{n})^3 r} \right]_{ret} \\ \mathbf{B} &= [\mathbf{n} \times \mathbf{E}]_{ret} \end{aligned} \quad (2.7)$$

Since any electromagnetic interaction propagates with the speed of light, we have to

take into account the time required for the electromagnetic field to propagate to the measured point. That is why the square bracket is evaluated at a time when the electromagnetic field was leaving the charge, the so called retarded time.

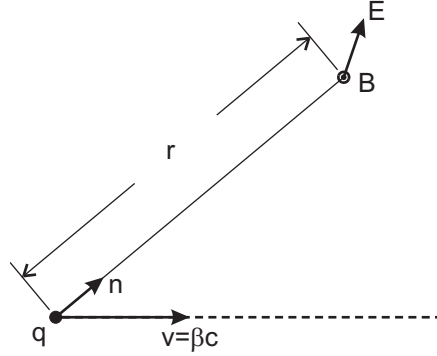


Figure 2.7: A relativistic electric charge q in an arbitrary motion $\mathbf{v}$ generates at a point $r\mathbf{n}$ away electric and magnetic fields described by the Liénard-Wiechert formula.

The first term in the bracket of equation (2.7) is associated with the speed and is called a "velocity field". Having a $1/r^2$ dependence, it is short range and this is the electromagnetic field accompanying the electron bunch. The second term is associated with acceleration. The "acceleration field" is generated only when a charge is accelerated. This is also called radiation. Because of the $1/r$ long-range dependence, only radiation can contribute to a non-vanishing flow of energy through a remote spherical surface enclosing the charge.

Although a charge in uniform motion does not radiate, the electric and magnetic field of an ultra-relativistic charge resembles that of a plane wave moving in the same direction, that is $B \perp E$ and $E = cB$.

This fact is exploited by a method of calculating the radiation emitted by highly relativistic charged particles in interaction with the condensed media, the pseudo-photon method [?, ?]. This method considers *the effect of a charged particle equivalent to that of a set of photons* of various frequencies, obtained by Fourier transform. The radiation emitted is just scattered pseudo-photons and one can sum over all their

interaction cross-sections to obtain the interaction cross section for the particle.

$$\sigma_{particle} = \int n_{\omega} \sigma(\omega) d\omega \quad (2.8)$$

Calculation of the interactions can be done either in real space or in the Fourier space. The choice between them is a matter of ease of calculation or an intuitive picture of phenomena. The magnetic field pulse associated with a relativistic electron bunch is equivalent to a superposition of frequency components up to a cutoff given by the inverse of the pulse duration. The intensity of these components can be quite high if measured reasonably ($100\mu m$) close to the bunch.

As an example let's take an electron bunch that is gaussian in all 3 directions. It has n electrons, σ_t duration and transversal dimensions $\sigma_x = \sigma_y = \sigma_r$. The magnetic field generated by the bunch moving with near the speed of light can be found making use of the Ampere's law:

$$B(r, t) = \frac{\mu_0 n e}{\sqrt{2\pi}\sigma_t} \frac{1 - e^{-\frac{r^2}{2\sigma_r^2}}}{2\pi r} e^{-\frac{t^2}{2\sigma_t^2}} \quad (2.9)$$

At distances r larger than the diameter of the bunch the magnetic field is almost the magnetic field around a straight current wire and has a dependence of $1/r$.

$$B(r, t) = \frac{\mu_0 I(t)}{2\pi r} = \frac{\mu_0 \frac{ne}{\sqrt{2\pi}\sigma_t} e^{-\frac{t^2}{2\sigma_t^2}}}{2\pi r} = B_{peak}(r) e^{-\frac{t^2}{2\sigma_t^2}} \quad (2.10)$$

$B_{peak}(r)$ is the peak intensity of the magnetic field pulse at a distance r from the center of the bunch. A plot of the magnetic field for a beam with parameters $\sigma_t = 1ps$, $\sigma_r = 1\mu m$, $n = 10^{10}$. High intensity magnetic fields are possible near the electron beam if this is focused well. At larger distances the focusing does not matter much, see figure 2.8

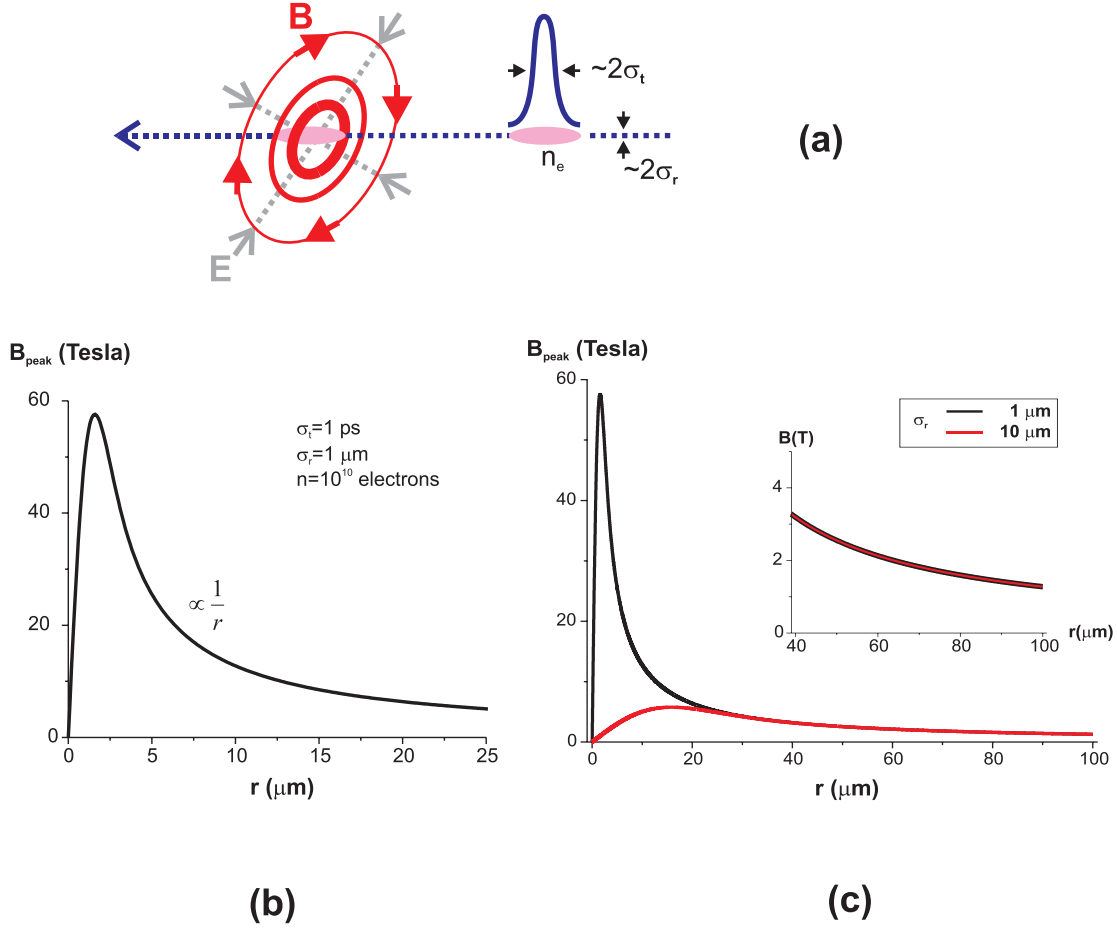


Figure 2.8: Spatial distribution of the magnetic field of a typical electron bunch. (a) The important parameters are the number of electrons in the bunch n , its transversal size σ_r and its duration σ_t . (b) In the usable space the magnetic field has a $1/r$ dependence. (c) Focusing enables high magnetic fields near the beam but it is not important at larger distances.

The frequency content of the pulse is easy to calculate. A magnetic field with a gaussian shape has the Fourier transform also a gaussian, as in figure 2.9.

$$B(r, t) = B_{\text{peak}}(r) e^{-\frac{t^2}{2\sigma_t^2}} \rightarrow B(r, \omega) = B_{\text{peak}}(r) \sigma_t e^{-\frac{\omega^2}{2(1/\sigma_t)^2}} \quad (2.11)$$

If the bunch is made shorter, keeping the same number of electrons, higher frequency

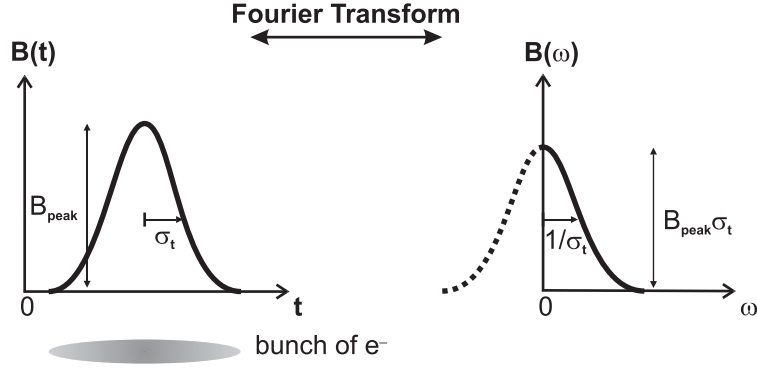


Figure 2.9: Frequency components of a gaussian magnetic field pulse with peak intensity B_{peak} and standard deviation σ_t . Only positive frequencies are meaningful.

components are added. By making the bunch shorter we get a high intensity field over a short period of time.

The Fourier component of the magnetic field is directly related to the number of pseudo-photons of that frequency. The energy of the electromagnetic field is stored as $n(\omega)$ quanta of energy $\hbar\omega$ per unit volume and frequency interval, see(2.12).

$$\frac{B(r, \omega)^2}{2\mu_0} d\omega = n(\omega)(\hbar\omega) d(\omega) \Rightarrow$$

$$n(\omega) = \frac{B(r, \omega)^2}{2\mu_0 \hbar\omega} = \frac{(B_{peak}(r)\sigma_t)^2}{2\mu_0 \hbar\omega} e^{-\frac{\omega^2}{(1/\sigma_t)^2}} \quad (2.12)$$

You may have noticed that the quantity $B_{peak}\sigma_t$ keeps appearing in formulas. From equation 2.10 we see that $B_{peak}\sigma_t$ is proportional to $q = ne$, the total amount of charge in the bunch, which is usually constant in our experiments.

2.3 Time scales of electromagnetic phenomena

As the time scale of the experiments become shorter, one has to understand what are the relevant processes involved. One such process is interaction of electromagnetic

field with matter. Maxwell's equations govern these processes and in SI units they are:

$$\nabla \times \mathbf{H} = \mathbf{j} + \frac{\partial \mathbf{D}}{\partial t} \quad (2.13)$$

$$\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t} \quad (2.14)$$

$$\nabla \cdot \mathbf{B} = 0 \quad (2.15)$$

$$\nabla \cdot \mathbf{D} = \rho_e \quad (2.16)$$

where the vectors and the scalars are

$\mathbf{H}$, magnetic field strength

$\mathbf{B}$, magnetic flux density

$\mathbf{D}$, electric flux density

$\mathbf{E}$, electric field strength

$\mathbf{j}$, free current density

ρ_e , volume density of free electric charges

Three more equations are required for a general solution. These equations are material dependent.

$$\mathbf{j} = \sigma \mathbf{E} \quad (2.17)$$

$$\mathbf{B} = \mu \mathbf{H} \quad (2.18)$$

$$\mathbf{D} = \epsilon \mathbf{E} \quad (2.19)$$

with

σ , electric conductivity

μ , magnetic permeability

ϵ , dielectric constant

If there is no time dependence we have simply have a static field

$$\nabla \times \mathbf{H} = \mathbf{j} \quad (2.20)$$

$$\nabla \times \mathbf{E} = 0 \quad (2.21)$$

The phenomenon of electromagnetic waves arises from the coupling of the laws of Faraday and Ampère through the time dependent terms $-\frac{\partial \mathbf{B}}{\partial t}$ and $\frac{\partial \mathbf{D}}{\partial t}$. The quasistatic laws are obtained by neglecting either of them in Maxwell's equations [?]. The electromagnetic wave propagation is neglected in either set. Quasistatic here

Electroquasistatic	Magnetoquasistatic
$\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t} \approx 0$ $\nabla \times \mathbf{H} = \mathbf{j} + \frac{\partial \mathbf{D}}{\partial t}$ $\nabla \cdot \mathbf{D} = \rho_e$ $\nabla \cdot \mathbf{B} = 0$	$\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t}$ $\nabla \times \mathbf{H} = \mathbf{j} + \frac{\partial \mathbf{D}}{\partial t} \approx \mathbf{j}$ $\nabla \cdot \mathbf{D} = \rho_e$ $\nabla \cdot \mathbf{B} = 0$

Table 2.1: Electro- and magnetoquasistatic equations.

means the finite speed of light is neglected and fields are considered to be determined by the instantaneous distribution of sources. The magnitude of the fields can be used to classify these equations.

The quasistatic approximation is justified only when the magnitude of the neglected terms is small compared to the other retained terms. For example, consider a system of *free space and perfect conductors*. If the system has a typical length scale L and the excitation has a characteristic time τ then we can approximate $\nabla \rightarrow 1/L$, $\frac{\partial}{\partial t} \rightarrow 1/\tau$. It turns out [?] that the error in the approximated fields are

$$\frac{E_{error}}{E} = \frac{\mu_0 \epsilon_0 L^2}{\tau^2} \quad , \quad \frac{B_{error}}{B} = \frac{\mu_0 \epsilon_0 L^2}{\tau^2} \quad (2.22)$$

Electroquasistatic	Magnetoquasistatic
Dominant Equations	
$\nabla \times \mathbf{E} = 0$ $\nabla \cdot \mathbf{D} = \rho_e$	$\nabla \times \mathbf{H} = \mathbf{j}$ $\nabla \cdot \mathbf{B} = 0$
Residual Equations	
$\nabla \times \mathbf{H} = \mathbf{j} + \frac{\partial \mathbf{D}}{\partial t}$ $\nabla \cdot \mathbf{B} = 0$	$\nabla \times \mathbf{E} = -\frac{\partial \mathbf{B}}{\partial t}$ $\nabla \cdot \mathbf{D} = \rho_e$

Table 2.2: Classification of quasistatic equations according to the magnitude of the fields

so the approximation is good when we have sufficiently slow time variation (large τ) and sufficiently small dimensions L

$$\frac{\mu_0 \epsilon_0 L^2}{\tau^2} \ll 1 \Rightarrow \frac{L}{c} \ll \tau \quad (2.23)$$

This is valid when an electromagnetic wave can propagate the characteristic length of the system in a time shorter than the time of interest. To determine which quasistatic approximation to use it helps to consider which fields are retained in the static limit ($\tau \rightarrow \infty$). For a given characteristic time, systems can often be divided in smaller regions small enough to be quasistatic, but dynamically interacting through their boundaries.

In the case of real systems with finite ϵ, σ, μ we have to refine the condition 2.23. Let's again consider a system with a typical length l and an excitation with a characteristic time τ . We normalize the quantities in the Maxwell's equations to their typical values.

$$\begin{aligned}
\epsilon(\mathbf{r}) &= \epsilon \underline{\epsilon} \quad , \quad \sigma(\mathbf{r}) = \sigma \underline{\sigma} \quad , \quad \mu(\mathbf{r}) = \mu \underline{\mu} \\
\mathbf{r} &= l \underline{\mathbf{r}} \quad , \quad t = \tau \underline{t} \quad , \\
\mathbf{E} &= \mathcal{E} \underline{\mathbf{E}} \quad , \quad \mathbf{H} = \mathcal{E} \sqrt{\frac{\epsilon}{\mu}} \underline{\mathbf{H}} \quad , \quad \rho = \frac{\epsilon \mathcal{E}}{l} \underline{\rho} \quad (2.24)
\end{aligned}$$

Then the Maxwell's equations, with the help of the material dependent equations, become

$$\begin{aligned}\underline{\nabla} \cdot \underline{\epsilon \mathbf{E}} &= \underline{\rho} \\ \underline{\nabla} \times \underline{\mathbf{H}} &= \frac{\tau_{em}}{\tau} \left(\frac{\tau}{\tau_e} \underline{\mathbf{E}} + \frac{\partial \underline{\epsilon \mathbf{E}}}{\partial t} \right) \\ &= \frac{\tau_m}{\tau_{em}} \underline{\mathbf{E}} + \frac{\tau_{em}}{\tau} \frac{\partial \underline{\epsilon \mathbf{E}}}{\partial t}\end{aligned}\tag{2.25}$$

$$\underline{\nabla} \times \underline{\mathbf{E}} = -\frac{\tau_{em}}{\tau} \frac{\partial \underline{\mathbf{H}}}{\partial t}$$

$$\underline{\nabla} \cdot \underline{\mu \mathbf{H}} = 0$$

The times involved here represent charge relaxation time τ_e , magnetic diffusion time τ_m and the transit time for an electromagnetic wave τ_{em}

$$\tau_e \equiv \frac{\epsilon}{\sigma}; \quad \tau_m \equiv \mu \sigma l^2; \quad \tau_{em} \equiv \frac{l}{c} = l \sqrt{\mu \epsilon}\tag{2.26}$$

As an example in copper, with $\sigma = 6 \times 10^7 \text{ } \Omega^{-1} m^{-1}$, $l = 0.3 \text{ mm}$, the times are $\tau_{em} = 10^{-12} \text{ s}$, $\tau_m = 7 \times 10^{-6} \text{ s}$, $\tau_e = 1.5 \times 10^{-19} \text{ s}$. The electromagnetic transit time is the geometric mean of the other two $\tau_{em} = \sqrt{\tau_e \tau_m}$, that is, it lies between τ_e and τ_m . The importance of various terms in Maxwell's equations is given by the following ratios

$$\frac{\tau_e}{\tau}; \quad \frac{\tau_m}{\tau}; \quad \frac{\tau_{em}}{\tau}\tag{2.27}$$

The picture 2.10 gives the domain of validity for the quasistatic approximation

As the excitation time becomes shorter, dynamical processes associated with charge relaxation, electromagnetic wave propagation and magnetic diffusion appear.



Figure 2.10: Ordering of the characteristic times of the electromagnetic phenomena on the excitation time axis. Left diagram describes system that can be treated with an electro-quasistatic approximation, while the right diagram shows the ordering for systems amenable to magneto-quasistatic approximation. τ_e is the charge relaxation time, τ_m magnetic field diffusion time, τ_{em} electromagnetic transit time.

2.4 Conductive boundary

Most magnetic media samples are metallic and therefore good conductors. The conduction electrons, being highly mobile, will tend to screen any electromagnetic fields inside a conductor. In a perfect conductors they move instantly in response to changes in the fields, no matter how rapid, to produce the correct surface charge density and surface current to screen the electric and magnetic field inside. The boundary conditions for a perfect conductor are

$$\begin{aligned}
 \mathbf{n} \cdot \mathbf{D} &= \Sigma \\
 \mathbf{n} \times \mathbf{H} &= \mathbf{J}_s \\
 \mathbf{n} \cdot (\mathbf{B} - \mathbf{B}_c) &= 0 \\
 \mathbf{n} \times (\mathbf{E} - \mathbf{E}_c) &= 0
 \end{aligned} \tag{2.28}$$

where $\mathbf{n}$ is the unit normal of the surface directed outward, Σ the surface charge, $\mathbf{J}_s$ the surface current and the subscript c refers to the fields inside the conductor. Just outside the surface only normal $\mathbf{E}$ and tangential $\mathbf{H}$ fields can exist, while inside the fields drop abruptly to zero as shown in figure 2.11.

The finite conductivity of a good conductor that is not perfect implies that the surface is not as effective in screening the magnetic field. In fact the penetration of the magnetic field is described by a diffusion type equation.

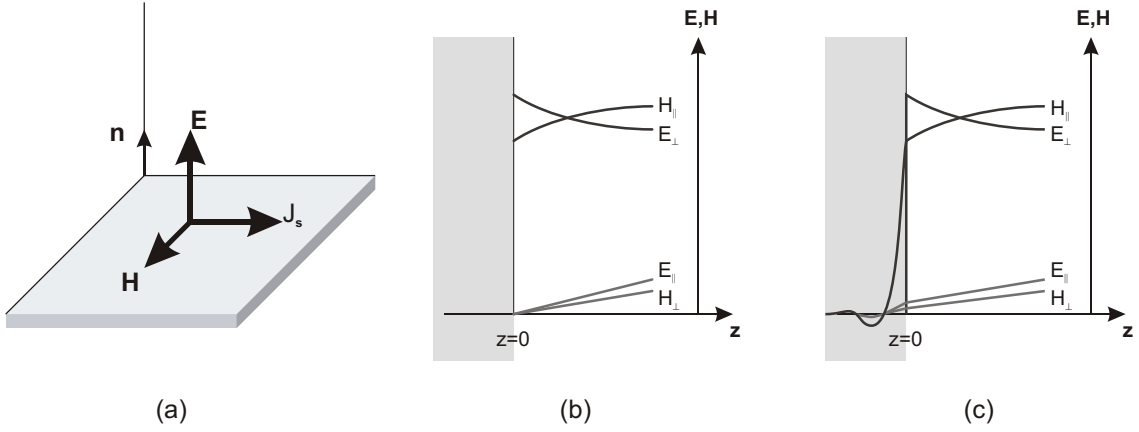


Figure 2.11: Fields traversing a conductive boundary. (a),(b) A perfect conductor has only normal electric field and tangential magnetic field just at the surface. (c) A good, but not perfect conductor allows the tangential magnetic field to penetrate inside over a skin depth distance. (The magnetic field plotted here sinusoidal time variation, hence the oscillatory behavior.)

From Ampere's equation 2.13, eliminating the electric field, we can deduce the following differential equation for magnetic field:

$$\epsilon\mu\frac{\partial^2 H_c}{\partial t^2} + \sigma\mu\frac{\partial H_c}{\partial t} = \Delta H_c \quad (2.29)$$

In good conductors σ is large and the conduction term dominates over the displacement term. The equation then becomes a classical diffusion equation.

$$\Delta H_c - \sigma\mu\frac{\partial H_c}{\partial t} = 0 \quad (2.30)$$

For a tangential sinusoidal (frequency ω) magnetic field $\mathbf{H}_{\parallel}$ outside the solution for $\mathbf{H}_c$ inside the conductor is

$$\mathbf{H}_c = \mathbf{H}_{\parallel} e^{-z/\delta} e^{iz/\delta} \quad (2.31)$$

where $\delta = \sqrt{2/(\mu\omega\sigma)}$ is the skin depth. The Faraday law requires that there is also

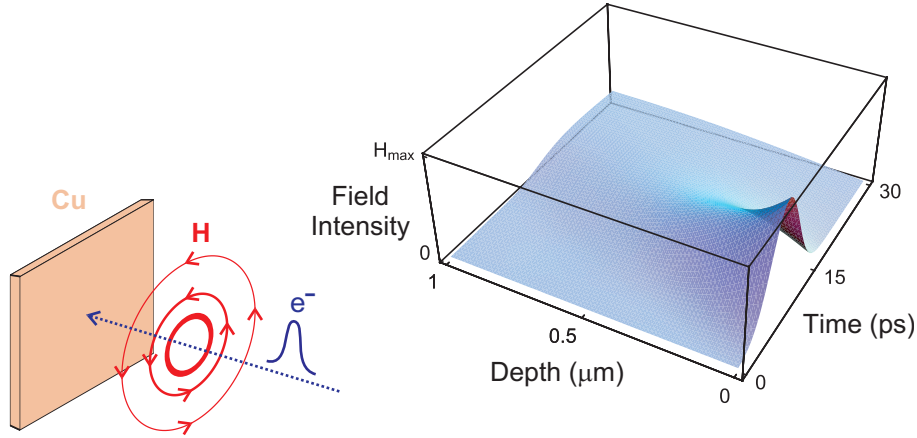
a small electric field associated with this magnetic field given by equation (2.32).

$$\mathbf{E}_c = \sqrt{\frac{\mu\omega}{2\sigma}}(1-i)(\mathbf{n} \times \mathbf{H}_{\parallel})e^{-z/\delta}e^{iz/\delta} \quad (2.32)$$

Using boundary condition for the electric field implies a similar small tangential electric field $\mathbf{E}_{\parallel}$.

The above solutions show an exponential decay and their amplitude is significant only on lengths a few times the skin depth. The magnetic field is much larger than the electric field as shown in 2.11. Because of the finite conductivity any perpendicular magnetic field will also penetrate the conductor, however, an evaluation using the Faraday law gives $\mathbf{B}_{\perp}$ on the same order of magnitude as $\mathbf{E}_{\parallel}$.

In first order one can approximate a gaussian pulse with a half period of a sinusoidal oscillation, but a numerical solution for the diffusion of a gaussian pulse associated with a relativistic electron beam is shown in figure 2.12 The skin depth



Magnetic field diffuses into copper

Figure 2.12: The magnetic field associated with an electron bunch diffuses into a conductive sample, a copper slab. If one is interested only in a thin layer at the surface (much thinner than $1\mu\text{m}$) the magnetic diffusion can be neglected and the magnetic field can be considered constant across its thickness.

in a typical metal like copper is of the order of microns for magnetic field pulse of

picoseconds duration. As one moves deeper under the surface, the magnetic field pulse is spread more and the maximum intensity is lower. However the time integral of the magnetic field remains the same, being proportional to the amount of charge in the beam.

2.5 Electric charge relaxation

A conductor reacts to any electric field and redistributes its charge to screen the it, eventually relaxing into an equilibrium state. The the electric charge relaxation equation (which can be derived from equations 2.13,2.16,2.17) and its solution are

$$\frac{\partial \rho_e}{\partial t} + \frac{\sigma}{\epsilon} \rho_e = 0 \quad , \quad \rho_e = \rho_{e0} e^{-\frac{t}{\tau_e}} \quad (2.33)$$

There is one correction to the above equations in the case of conductors. The time $\tau_e \approx 10^{-19} s$ for copper seems very short and nonphysical, after all, light travels only $0.3 \text{\AA}$ during that time. Ohm's law used in free electric charge equation 2.33 is valid only for times larger than the time between collisions τ_c . The assumption of a good conductor is reasonable only if $\tau \gg \tau_c$. For copper $\tau = 5 \times 10^{-14} s$, so the above considerations hold at least up to frequencies in infrared spectrum.

The simplest model describing charge relaxation can be derived from the Drude model of electrical conduction. According to this model the motion of conduction electrons is described by the equation:

$$m\ddot{\mathbf{r}} = -e\mathbf{E} - m\dot{\mathbf{r}}/\tau_c \quad (2.34)$$

that has a solution

$$\mathbf{r} \sim \mathbf{e}^{-\frac{t}{2\tau_c} \pm i\omega_p t} \quad (2.35)$$

with τ_c the time between collisions and ω_p the plasma frequency ($\omega_p = \sqrt{\frac{ne^2}{m\epsilon}} = \sqrt{\frac{\sigma}{\tau\epsilon}}$). Any deviation from neutrality within the conductor will be restored on the time scale of τ_c in a damped oscillatory process ([?]).

The electric field is screened very well inside metal thin film samples. This process takes place very fast with the screening charge oscillating with plasma frequency and being damped in times comparable to the collision time of the electrons, see eq. 2.35. The surface charge is located in a very thin layer of about $\pm 2 \text{ \AA}$ at the surface of the metal [?], as in figure 2.13. .

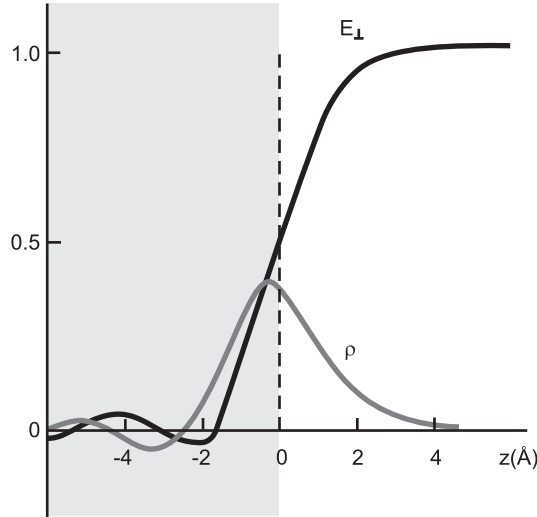


Figure 2.13: Surface electrical charge density $\rho(z)$ and normal electric field $E_{\perp}(z)$ distributions at the surface of a conductor confined to $z < 0$.

In the case of insulators and semiconductors the electric field polarizes the matter and for a high enough field the phenomenon of dielectric breakdown can occur. The electric field generated by the electron beam has an amplitude related to the amplitude of the magnetic field $\mathbf{B} = \frac{\beta}{c} \times \mathbf{E}$. So, for a magnetic field of 1 Tesla and $\beta \simeq 1$, the electric field has a value of $3 \times 10^8 \text{ V/m}$. For comparison the electric breakdown in air occurs at an electric field of $\approx 3 \times 10^6 \text{ V/m}$ while for GaAs it occurs at $\approx 4 \times 10^7 \text{ V/m}$.

As one makes the electron bunch shorter the charge linear density increases and

so does the electric field, see 2.6. As a consequence, the electric field exceeds the breakdown limit over a larger area. One can observe the damaged area in figure 2.1 in a sample with GaAs as substrate.

2.6 Screening for a relativistic electron bunch

The screening of the electric field and magnetic field of a relativistic electron bunch by a metallic sample can be visualized intuitively with the method of image charges.

As a electron bunch approaches of the conductive sample the electric field associated with the bunch will start to move electrons inside the sample. Very quickly they reach such a position as to make a zero total electric field inside the sample. The same electric field at the surface of the sample is achieved if one removes the sample and replaces it with distribution of charge that is a mirror image of the electron bunch. Figure 2.14 shows some model cases of charge distribution close to a conductive surface and their field lines.

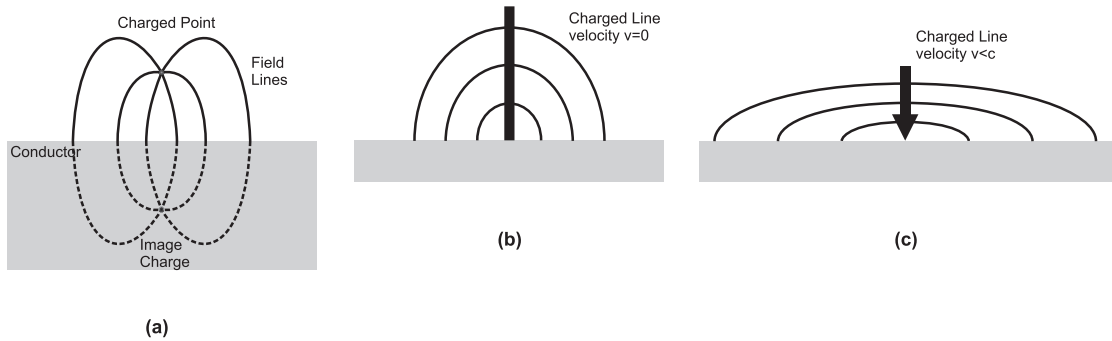


Figure 2.14: Method of image charges applied to (a) point charge (b) line charge (c) moving line charge close to a conductive surface. In all cases the electric field lines are perpendicular to the conductive surface. The conductor behaves as an opposite image charge.

An electron bunch has the electric field perpendicular to the sample because the field lines are spread over a large area, and so its surface charge associated with this

field. The magnetic field cannot be screened by these image charges because both the moving electron bunch and its image produce a current in the same direction, see figure 2.15. Only the surface eddy currents can screen the magnetic field.

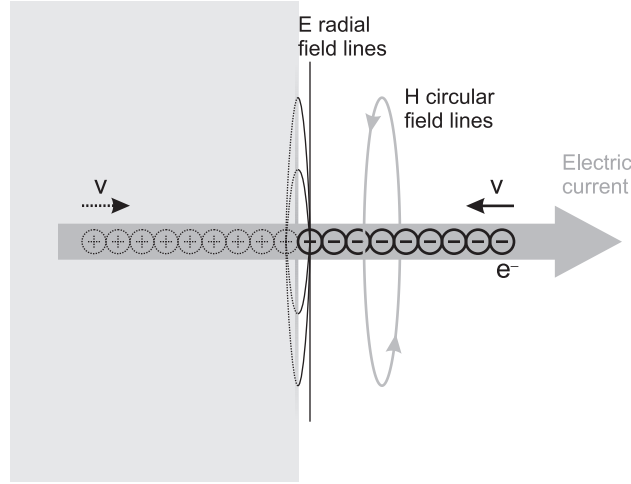


Figure 2.15: An illustration of Electric and magnetic field lines near the surface of a conductor for a beam of relativistic electrons. The moving positive image charges are equivalent to a current in the same direction as that produced by the incoming electrons.

When an experiment calls for a large electric field perpendicular to a conductive sample the electron bunch has to fly over the surface of the sample. This can also be understood from the fact that in figure 2.3 the electric field in the direction of motion is $1/\gamma^3$ the electric field transversal to the direction of motion.

2.7 Energy loss of the electron beam in matter

As high energy electrons pass through a sample they interact with the matter and lose energy. Part of that lost energy is dumped into the damaged area at the impact point.

The total stopping power (energy loss per unit length of path) of electrons in

matter be written as the sum of two terms [?], one due to ionization by collision and the other due to radiation (bremsstrahlung):

$$-\frac{dE}{dx} = \left(-\frac{dE}{dx}\right)_c + \left(-\frac{dE}{dx}\right)_r \quad (2.36)$$

.

The energy loss due to collisions is given by the Bethe-Bloch equation:

$$\begin{aligned} \left(-\frac{dE}{dx}\right)_c = & \frac{Ze^4n}{8\pi\epsilon_0^2m_ev^2} \left[\ln \frac{m_ev^2K}{2I^2(1-\beta^2)} - \left(2\sqrt{1-\beta^2} - 1 + \beta^2\right) \ln 2 \right. \\ & \left. + 1 - \beta^2 + \frac{1}{8} \left(1 - \sqrt{1-\beta^2}\right)^2 \right] \end{aligned} \quad (2.37)$$

where Z is the atomic number of the absorber, e the charge of electron, n the number of atoms per unit volume, m_e the static mass of electron, $v = \beta c$ the speed of electrons, K the kinetic energy of electrons, I the mean ionization potential of the absorber.

The energy loss due to radiation is

$$\left(-\frac{dE}{dx}\right)_r = \frac{\alpha n E Z (Z+1) e^4}{4\pi^2 \epsilon_0^2 (m_e c^2)^2} \left[\ln \frac{2E}{m_e c^2} - \frac{1}{3} \right] \quad (2.38)$$

, where $E = K + m_e c^2$ is the energy of the electron and $\alpha \approx 137$ is the fine constant.

The radiative contribution to the energy loss becomes important only at high energies, typically above 10 MeV. The ratio between two contributing stopping powers is approximately

$$\frac{\left(-\frac{dE}{dx}\right)_c}{\left(-\frac{dE}{dx}\right)_r} = \frac{EZ}{1600m_e c^2} \quad (2.39)$$

. At large energies the radiative loss processes dominates, see figure 2.16 where the stopping power is a measure of energy lost per unit length. . However, in general, matter is much more transparent to electromagnetic radiation than to charged particles and the radiation part of the energy loss does not remain in the sample area.

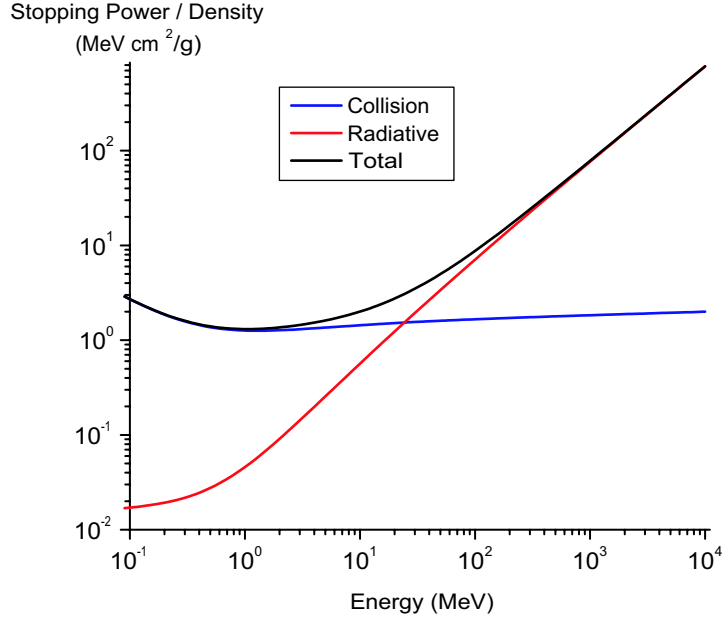


Figure 2.16: Stopping power of copper for electrons is dominated by radiative loss at high energies. The collision loss remains approximately at the same level. Note that here we have divided stopping power by density.

Thus the main contributing factor to the damage area is the absorption of the collision part of the energy loss.

For copper with density $\rho = 9\text{g/cm}^3$ and an electron energy of 30 GeV the total stopping power is $\approx 20\text{GeV/cm}$, while the collision part is $\approx 2.4\text{MeV/cm}$. An electron beam with 10^{10} electrons will deposit an energy of $\approx 4\text{mJ}$ in a path of 1cm . These are only approximate numbers because they neglect the effect of multiple scattering in altering the path.

If the electron beam is focused to spots of the order of microns size the collision loss of the electrons will raise the temperature of the impact point on the sample, and most of the energy will be lost by radiation. A small part of it will be conducted to adjacent area but, since conduction is slow, it does not transport much energy before the impact point is cooled off by radiation emission. Thus the damaged area is restricted around the impact point.

Chapter 3

Experimental Setup

The velocity electromagnetic field is short-range. In order to observe its effects on the thin film sample one has to focus the beam both to reduce the damage to a small area and to increase the intensity of the electromagnetic field close to that area. For the amount of charge in the electron bunch of the order of several nanocoulombs, the magnetic field is useful on a length scale of several hundred microns ($B \propto q/r$ see 2.10). It is then desirable to keep the focus below tens of microns.

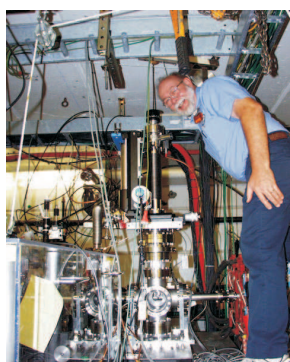


Figure 3.1: Experimental setup and location. (Jerry Collet, here standing near the whole apparatus, helped in the chamber design and assembly.)

For such a fine focus a good manipulator is needed for moving the sample into the beam in the right position. The one used on our experiment was an *Omniax* type

translator with an XY table. The stepper motors had 20,000 steps per revolutions with the motion transmitted as 1 rotation per mm for XY table while the vertical Z translator was driven by a screw with 5 rotations per mm. The manipulator (figure 3.1) was commanded by a *Compumotor* controller that communicated with an outside computer through an Ethernet cable. During the actual run, all personnel has to be outside the accelerator tunnel for radiation safety reasons. The user interface was written in *Labview* and was structured as a state machine, the states corresponding to different stages of the experiment (focusing of the beam, exposure of the samples park in storage position etc.)

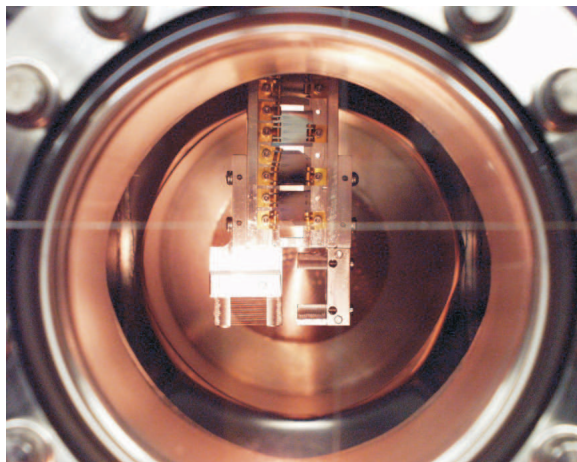


Figure 3.2: Wire scanners for monitoring the beam size and position. There are two groups of wires for vertical and horizontal directions. Some of the samples are visible in the upper part of the picture. The picture is taken from a window into the vacuum chamber situated on the accelerator line.

Also there is a need to find where the electron beam is with respect to the sample holder. Once an absolute reference point is found the sample can be exposed easily at the desired points using incremental steps from that reference point. The size and position of the beam are found by using wire scanners, see figure 3.2. Carbon and tungsten wire were used with diameters between $5 - 35 \mu m$. Some of the thinner

wires broke after on or two shots under a short pulse of 100fs and a focus of $20\text{ }\mu\text{m}$. The size of the beam is estimated after the intensity curve of the gamma ray radiation generated when the electron beam is swept across a wire.

The vacuum inside the whole chamber has to be very good (better than $10^{-7} - 10^{-8}\text{torr}$) otherwise the electron beam will ionize the gas inside making a plasma which is not good for the sample because the sample is heated and etched by the plasma. The first experiments were unable to see a good magnetic pattern precisely because of this damaging effect of a poor vacuum. Although a magnetic pattern was recorded, the magnetic film was destroyed by the interaction with ionized gases.

The vacuum chamber is a six-way cross vacuum fitting. Two of the side ports were connected to the accelerator, the top port was used for loading the samples on a holder (figure 3.3) and two other side ports were windows.

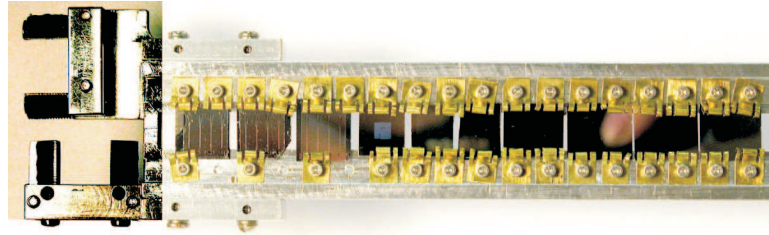


Figure 3.3: Overview of a typical sample holder with 10 samples loaded and the wire scanners attached to left side of the picture.

As the electron bunch goes through the sample it generates secondary electrons that exit the sample leaving it positively charged. Grounding the sample holder is essential to prevent the charging of the samples and the subsequent damaging sparks. Fragile samples can even break under stresses caused by excessive charges. Some magnetic films deposited on insulating glass substrate were rendered unusable because the substrate fractured in pieces. From this perspective a metallic substrate would be better.

Chapter 4

Magnetic Imaging

4.1 Magneto-optic Effects

The magneto-optic effects are due to the interaction of light and electrons of the media through which light propagates. Visible light does not penetrate far into the metals and thus the magneto-optic methods are surface methods suitable for the study of thin films. Although the magneto-optic effects are usually associated with visible light they may be seen in the whole spectrum of electromagnetic radiation.

These effects reflect the influence of an applied magnetic field or a spontaneous magnetization on the polarization state and intensity of light. The changes of the emergent light with respect to incident light can be in amplitude (*dichroism*) or in phase (*birefringence*). The emergent light may be transmitted (Faraday and Voigt effects) or reflected (Kerr effect), shown in figure 4.1.

All types of materials show magneto-optic effects: diamagnetic, paramagnetic and ferromagnetic materials. These effects can be attributed to off-diagonal terms in the dielectric or magnetic susceptibility tensor. In first order the effects are due to the interaction of the electric field of the light with the electrons. The orbital motion of the electrons under the electric field is influenced by the spin-orbit coupling and in

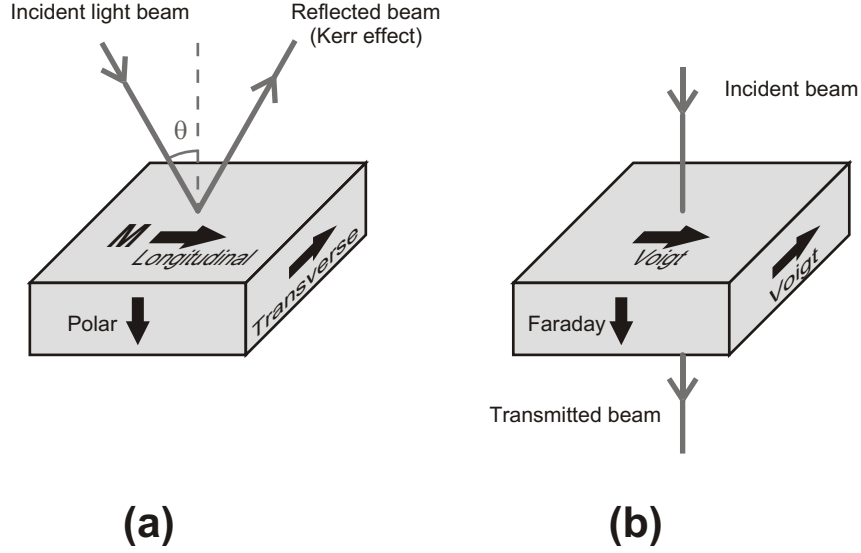


Figure 4.1: Magneto-optic effects. (a) Kerr effect in different geometries (orientation of magnetization with respect to the surface and plane of incidence). (b) Faraday and Voigt effects for transmitted light

the case of a ferromagnet all spins are aligned, leading to a large magneto-optic effect.

For example, to first order in magnetization $\mathbf{M}$, a cubic or isotropic material has the following dielectric susceptibility tensor ϵ :

$$\epsilon = \epsilon_0 \begin{bmatrix} 1 & -iQM_z & iQM_y \\ iQM_z & 1 & -iQM_x \\ -iQM_y & iQM_x & 1 \end{bmatrix} \quad (4.1)$$

where ϵ_0 is the dielectric constant in the absence of magnetization that has M_i components. Q is a parameter that reflects the different behavior of right and left circularly polarized light. When $\mathbf{M}$ reverses the off-diagonal terms change sign and thus, the magneto-optic effects also change sign. A detailed calculation involves solving the Maxwell equations with the appropriate boundary conditions (for reflected and transmitted light), but the main idea is that an incident electric field $\mathbf{E} \parallel \mathbf{M}$ produces

a dielectric polarization $\mathbf{P} \nparallel \mathbf{E}$ changing the polarization of the emergent radiation.

In general, reflection or transmission of light from a surface changes the polarization of light even without the presence of magnetization. However, if the light is linearly polarized in the plane of incidence (p-polarization) or perpendicular to it (s-polarization), there is no change of polarization due to the surface. Then, if the material is magnetic, the output may be elliptical (ϕ') and rotated (ϕ'') with respect to the initial polarization direction as shown in figure 4.2. The rotation and

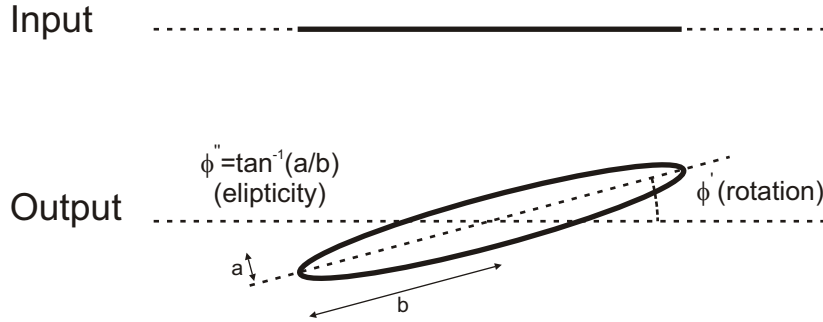


Figure 4.2: Change in polarization state due to magneto-optic effects.

ellipticity are usually taken to be the real and imaginary parts of a complex rotation $\phi = \phi' + i\phi''$. As an example, Kerr effect in iron at room temperature and 633 nm light has $\phi = 0.14^\circ + i0.07^\circ$ in longitudinal geometry and 45° incidence while $\phi = 0.63^\circ - i0.47^\circ$ in polar geometry and normal incidence. Measurement conditions must be specified since the measured angle varies with refractive index, the angle of incidence, the temperature and the wavelength.

4.2 Scanning Electron Microscopy

Another method of imaging the magnetization of ferromagnetic thin films is by detecting the polarization of secondary electrons. A scanning electron microscope is well suited for this as it can make a small scanning spot size of the incident electrons that generate the secondary electrons. Scanning Electron Microscopy with Spin Analysis (SEMPA) images the magnetization by measuring the spin polarization of secondary electrons that is directly related to the magnetization of the sample. Measurements of the magnetization are intrinsically independent of the topography, but the magnetic and topographic maps are measured simultaneously. Because of the small (nanometers) secondary electron escape depth the method is surface sensitive.

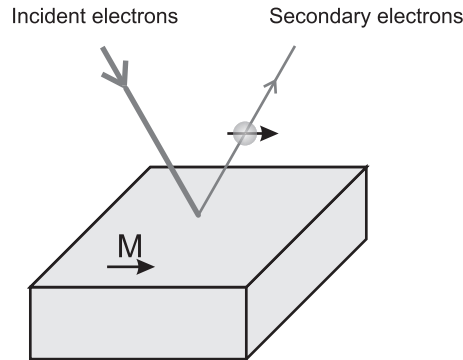


Figure 4.3: The principle of scanning electron microscope with polarization analysis: An unpolarized monoenergetic electron beam, focused by electromagnetic lenses, scans across the ferromagnetic surface. At each scanned position, spin-polarized secondary electrons are created near the surface, emitted into vacuum and transferred to the spin analyzer by electrostatic lenses.

4.3 Photoemission electron microscopy

X-ray photons impinging on a sample cause secondary electrons to be emitted from the surface. One can then use regular electron optics to image the place where these

electrons originated (figure 4.4). Absorption of photons and subsequent generation of electrons can tell a lot of things about sample. The contrast in the image can be elemental, chemical, magnetic or topographical.

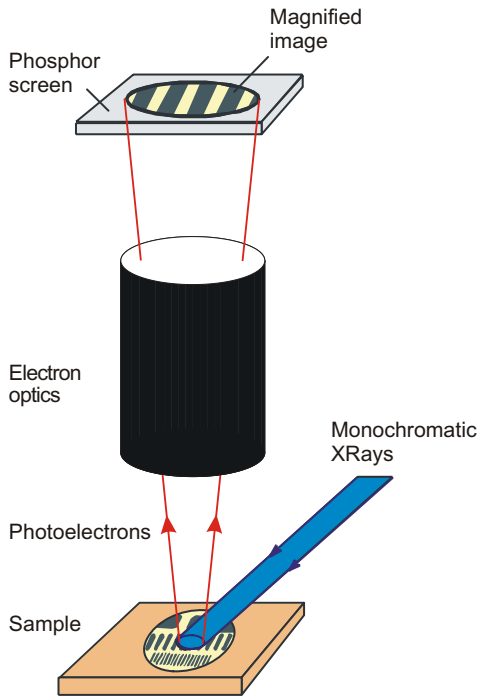


Figure 4.4: The principle of photoemission electron microscope with X-rays: An X-ray photon beam is shine on the sample and the secondary electrons pass through electron optics giving a magnified image on a phosphor screen.

When studying ferromagnetic samples the phenomenon of X-ray magnetic dichroism is employed. Circularly polarized photons are shined on the sample and absorbed by atoms promoting the electrons in the core level to an empty valence band level. The subsequent decay of the core level hole generates the secondary electrons imaged by the electron optics. The absorption is sensitive to the magnetization orientation because the electronic transition conserves the electron spin while the valence band is spin split by the exchange interaction in the ferromagnetic sample and the core level is also split by spin-orbit interaction (figure 4.5). The absorption process is a miniature spin polarizer-analyzer experiment (made possible by the conservation of angular momentum).

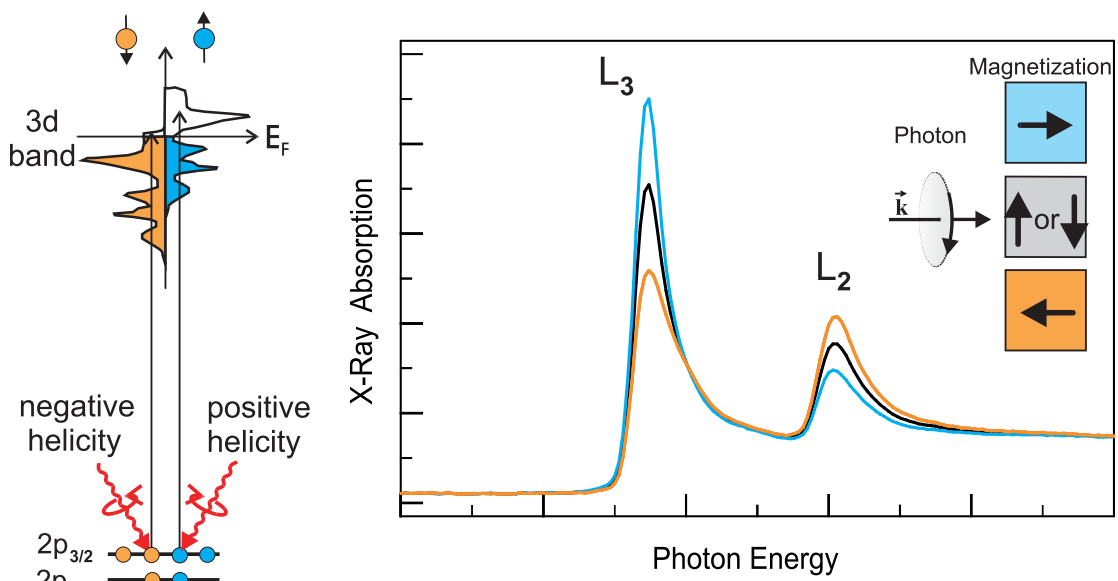


Figure 4.5: Illustration of the XMCD effect: The angular momentum and the energy carried by the photon is transferred to a core level electron which is promoted to an empty valence band level. There are more empty levels of one spin orientation due to the exchange interaction and so the absorption of the photon is dependent on the orientation of the magnetization.

Chapter 5

Magnetization Dynamics Equation

Magnetic materials contain a collection of magnetic moments (dipoles) and the physics of magnetism tries to explain the behavior of this collection of moments under a variety of conditions and excitations. The most important behavior of a magnetic moment is the precession in a magnetic field.

The magnetic moment $\mathcal{M}$ feels a torque from the magnetic field $\mathbf{B}$ acting on it, torque given by

$$\mathcal{T} = \mathcal{M} \times \mathbf{B} \quad (5.1)$$

An angular momentum $\mathbf{L}$ is always associated with the magnetic moment, one being proportional to another (with magneto-mechanical ratio γ)

$$\mathcal{M} = \gamma \mathcal{L} \quad (5.2)$$

and since we know that $\mathcal{T} = d\mathcal{L}/dt$ the equation of motion for the magnetic moment is

$$\frac{d\mathcal{M}}{dt} = \gamma \mathcal{M} \times \mathbf{B} \quad (5.3)$$

This is the basic equation of motion for a magnetic moment, but the hard part is

to find the magnetic field acting on the magnetic moment. The field of micromagnetics simulates the dynamics of an ensemble of magnetic moments, modelling the interaction of the magnetic moment with the environment as an effective field.

When one has a lot of magnetic moments it is easier to use the continuum approximation when one deals with the magnetic moment density, also known as the magnetization $\mathbf{M} = \mathcal{M}/V$. With magnetic induction expressed as $\mathbf{B} = \mu_0 \mathbf{H}_{eff}$ the equation 5.3 becomes

$$\frac{d\mathbf{M}}{dt} = \gamma \mu_0 \mathbf{M} \times \mathbf{H}_{eff} \quad (5.4)$$

The dissipation of angular momentum is usually modelled as a phenomenological damping term and a simple way is to take it proportional to $d\mathbf{M}/dt$ [?] like in ohmic dissipation

$$\mathbf{H}_{eff} = \mathbf{H} - \frac{\alpha}{\mu_0 \gamma M_s} \frac{d\mathbf{M}}{dt} \quad (5.5)$$

The remaining part $\mathbf{H}$ includes the anisotropy, exchange, dipolar (from neighboring magnetic moments) and external magnetic fields which will be addressed later. The equation 5.4 then becomes Landau-Lifshitz-Gilbert equation

$$\frac{d\mathbf{M}}{dt} = \gamma \mu_0 \mathbf{M} \times \mathbf{H} + \frac{\alpha}{M_s} (\mathbf{M} \times \frac{d\mathbf{M}}{dt}) \quad (5.6)$$

which can be transformed into an explicit equation for $d\mathbf{M}/dt$, known as Landau-Lifshitz equation.

$$(1 + \alpha^2) \frac{d\mathbf{M}}{dt} = \gamma \mu_0 \left[\mathbf{M} \times \mathbf{H} + \frac{\alpha}{M_s} \mathbf{M} \times (\mathbf{M} \times \mathbf{H}) \right] \quad (5.7)$$

Historically equation 5.7 was derived first, the damping term being introduced in such a way as to relax the precessing magnetization into the field direction as shown in figure . The dimensions can be taken out of the equation 5.7 by normalizing to M_s

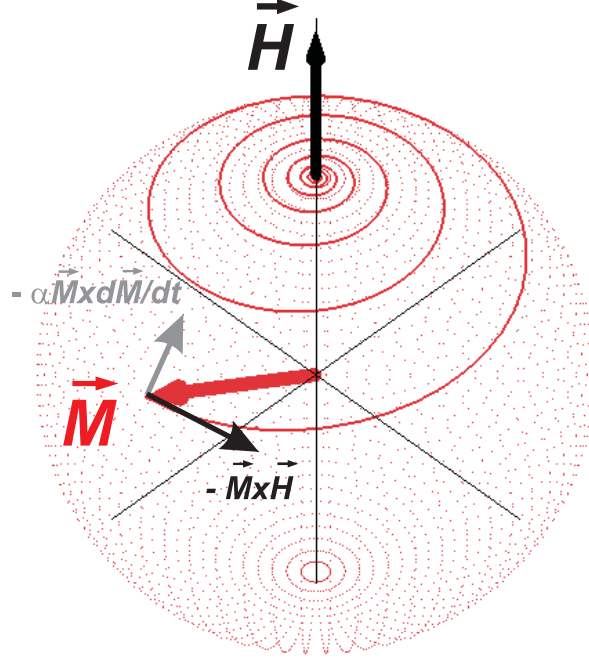


Figure 5.1: Directions of the precessional and damping torques for magnetization in a constant magnetic field. The damping torque eventually brings the magnetization into the direction of the field.

$\mathbf{m} = \mathbf{M}/M_s$, $\mathbf{h} = \mathbf{H}/M_s$ and using a time normalized to $\tau = t/(|\gamma|\mu_0 M_s)^{-1}$

$$(1 + \alpha^2) \frac{d\mathbf{m}}{d\tau} = -\mathbf{m} \times \mathbf{h} - \alpha(\mathbf{m} \times (\mathbf{m} \times \mathbf{h})) \quad (5.8)$$

For an electron γ is negative hence the minus sign in the above equation.

The magnetic field $\mathbf{H}$ can be obtained if one interprets the force acting on a magnetic moment $\mathcal{M}$ as the negative gradient of a potential energy $\mathcal{U} = -\mu_0 \mathcal{M} \cdot \mathbf{H}$. The torque is then $\mathcal{T} = d\mathcal{U}/d\theta$, where θ is the angle between $\mathcal{M}$ and $\mathbf{H}$. This torque is the precessional torque $\propto \mathbf{M} \times \mathbf{H}$ in figure 5.1. The damping torque just dissipates the excess potential energy to bring the system to the lowest energy configuration, i.e. the magnetization parallel to the magnetic field

The variation of the free energy density U with respect to magnetization direction $\mathbf{M}$ will give the magnetic field $\mathbf{H}$.

$$\mathbf{H} = -\frac{1}{\mu_0} \frac{dU}{d\mathbf{M}} \quad (5.9)$$

The part of free energy density U where $\mathbf{M}$ enters consists of the *magnetic energy* in the external field, the *magnetostatic energy* from interaction between different parts of the magnetized body, the *anisotropy energy* with respect to crystallographic axes and the *exchange energy* between neighboring regions with different orientation of the magnetization. Thus the field $\mathbf{H}$ is

$$\mathbf{H} = \mathbf{H}_{extern} + \mathbf{H}_{magnetostatic} + \mathbf{H}_{anisotropy} + \mathbf{H}_{exchange} \quad (5.10)$$

The corresponding energy densities are [?] :

$$U_{extern} = -\mu_0 \mathbf{M} \cdot \mathbf{H}_{extern} = -\mu_0 M_s^2 \mathbf{m} \cdot \mathbf{h}_{extern} \quad (5.11)$$

$$U_{magnetostatic} = -\frac{\mu_0}{2} \mathbf{M} \cdot \mathbf{H}_{demag} = -\frac{\mu_0}{2} M_s^2 \mathbf{m} \cdot \mathbf{h}_{demag} \quad (5.12)$$

$$U_{anisotropy} = -K_u (\mathbf{m} \cdot \mathbf{u}_{uniaxial})^2 + K_{cubic} (m_x^4 + m_y^4 + m_z^4) \quad (5.13)$$

$$U_{exchange} = -A (\nabla \mathbf{m})^2 \quad (5.14)$$

where K_u , K_{cubic} are the uniaxial and cubic anisotropy energy densities, A the exchange constant and the H_{demag} is the demagnetizing field calculated from the magnetic potential of all other parts of the magnetic body:

$$\mathbf{H}_{demag} = -\nabla_{\mathbf{r}'} \left[\frac{1}{4\pi\mu_0} \int \frac{\rho(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} d\mathbf{r}' \right] \quad (5.15)$$

Most of the computation time in micromagnetics is spent in computing 5.15 because the integrand is long range and slow varying. The convolution integral is more efficiently calculated using Fast Fourier Transform techniques.

The dynamics described by the Landau-Lifshitz equation conserves the magnitude of magnetization, an approximation which is true in many systems. When spin-waves are generated the magnetization is reduced in amplitude and one needs an additional parameter to describe this process. The Bloch-Bloembergen equation [?] has such a term but only applies to small angle perturbations as in ferromagnetic resonance.

$$\frac{M_{x,y}}{dt} = \gamma\mu_0 [\mathbf{M} \times \mathbf{H}]_{x,y} - \frac{M_{x,y}}{T_2} \quad (5.16)$$

$$\frac{M_z}{dt} = \gamma\mu_0 [\mathbf{M} \times \mathbf{H}]_z - \frac{M_z - M_s}{T_1} \quad (5.17)$$

There is a direct relation [?] between the transversal relaxation time T_2 and α in equation 5.7

$$\frac{1}{T_2} = \alpha|\gamma|\mu_0 M_s \mathbf{h} \cdot \mathbf{m} \quad (5.18)$$

There is no equivalent in the Landau-Lifshitz equation for the longitudinal relaxation time T_1 , however the Landau-Lifshitz equation is better suited to describing the process of switching the magnetization direction as it is valid for large angle perturbations.

Chapter 6

Experiments with In-plane Magnetic Thin Films

6.1 Introduction

The bottleneck of magnetization dynamics is established by the necessity to conserve angular momentum whenever the magnetization M changes direction or magnitude. After an external excitation the spin system will ultimately equilibrate with the lattice on a time scale of several hundred picoseconds ($1 \text{ ps} = 10^{-12}\text{s}$), as measured through the line width of ferromagnetic resonance (FMR). Experiments based on precessional switching of M are compatible with the FMR derived dissipation [?, ?, ?, ?]. Applying the fastest conventional magnetic field pulses of $\approx 10^4 \text{ A/m}$ amplitude and $\approx 100 \text{ ps}$ duration [?, ?, ?, ?, ?], M will switch once performing a complex motion induced by the simultaneous action of the pulse and the anisotropy fields. It is difficult to evaluate the energy and angular momentum dissipated in such a single complex switching process.

Our experiment separates the initial deposition of energy and angular momentum into the spin system from the ensuing slower magnetic switching and dissipation

process, by using the extremely fast and powerful magnetic field pulse generated by highly relativistic electrons [?, ?, ?]. The field pulse amplitude varies across the sample thereby producing a large magnetic pattern. This pattern, revealed by magnetic microscopy, consists of a number ν of regions where M has switched its original direction. The location of the boundaries between the regions reveals the energy required for the switching, but owing to the internal clock provided by the precession of M also corresponds to well defined times t_ν at which the switching occurred. We find that the dissipation of the spin angular momentum increases strongly after the first switch, exposing the opening of a new dissipation channel, which we associate with transfer of energy and angular momentum from the uniform magnetization precession mode to higher spin wave modes. In agreement with the recently developed quantitative theory [?], we find that this channel becomes less effective with decreasing film thickness due to reduction of the phase space for suitable spin waves. Our experimental results reveal a larger dissipation than predicted with state-of-the-art numerical simulations, but they do not exhibit the ultrafast dissipation claimed in pulsed laser excitation.

6.2 Experimental details

Prior to the field pulse, the magnetization of the film, M , is oriented along the easy direction which we assume to lie in the xy plane of the film, along the x -axis. A model of the dynamics is illustrated in picture 6.1. In step one, the sample is excited by the magnetic field pulse generated with a bunch of highly relativistic electrons from the linear accelerator, see table 6.1. The electron beam travels along z , perpendicular to the film plane and as it traverses the metallic film, its electric field is screened at the fs -time scale. The magnetic field B penetrates the film because the skin depth is much larger than the film thickness. It is oriented perpendicular to the beam axis,

Property	Value
Energy of electrons	28 GeV
Number of electrons	$(1.0 - 1.4) \times 10^{10}$
Cross section (gaussian profile with $\sigma_x \times \sigma_y$)	$9 \times 6 \mu m$
Pulse length (gaussian profile with σ_z)	0.63 mm
Pulse duration ($\sigma_t = \sigma_z/c$)	$2.3 \times 10^{-10} s$
Peak magnetic field $B_p(Tesla)$ at distance $R(\mu m)$	$B_p = (59.1 - 82.1)/R$

Table 6.1: Some characteristics of the electron beam used in the experiment using in-plane media.

resembling the familiar circular field generated by a straight current carrying wire. The torque exerted by B on the magnetic moments makes them precess out of the film plane during the field pulse. The angle of precession is

$$\varphi = \int \omega dt = \int \gamma B_y(t) dt \propto Q x/r^2 \quad (6.1)$$

where ω is the precession frequency, $r = [x, y, z]$ the position vector with respect to the impact point, Q the total charge of the electron bunch. φ lies in the range $10^\circ - 25^\circ$ in the present experiments.

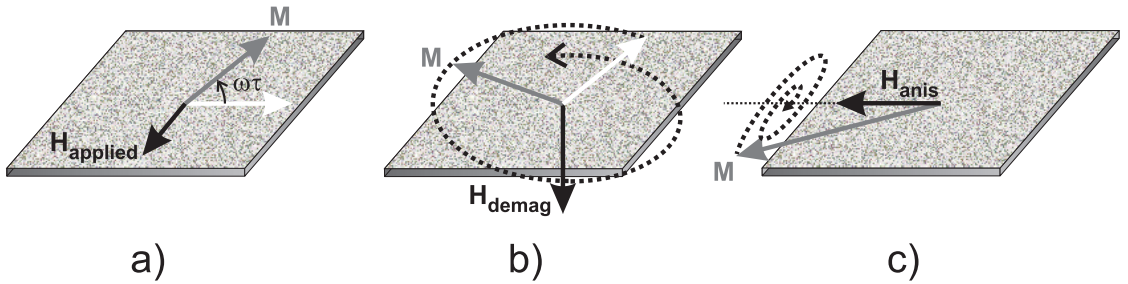


Figure 6.1: An illustration of the three step model for the in-plane media. (a) Magnetization vector is brought out the sample plane by the magnetic field of the electron bunch passing through. (b) The demagnetization field created in the previous step makes the magnetization precess around an axis perpendicular to the sample. (c) As the precession around the demagnetization field damps out, the anisotropy takes charge of the motion and the magnetization relaxes into the easy axis.

In the next step, starting at the end of the field pulse, M precesses around the demagnetizing field H_{demag} generated along the z -axis by the out-of-plane rotation of M during excitation. In this precession, a large angle $90^\circ - \varphi$ is enclosed between H_{demag} and M , distinguishing it from that in FMR where the precession angle is very small. In the large angle precession, the in-plane component M_x oscillates periodically between the two easy directions. Owing to the damping of the precession, M spirals back into the plane of the film until it can no longer overcome the anisotropy barrier imposed by the uniaxial, in-plane crystalline anisotropy energy K_u . Then, lastly M oscillates about the in-plane uniaxial anisotropy field $H_{ani,x} = 2K_u/M$ until it comes to rest in either the initial direction along x , or the direction opposite to it.

If $K_\perp$ is the energy density of the total perpendicular anisotropy, then the Zeeman energy density deposited in the spin system by the magnetic field pulse is given by

$$E = K_\perp \sin^2 \varphi \quad (6.2)$$

where we have neglected higher order anisotropies because they turn out to have a negligible effect. The energy $E(\varphi_1)$ to induce the first switch is given by the energy K_u to surmount the anisotropy barrier and the damping loss in the precession of M about H_{demag} by 90° to reach the anisotropy barrier. After that, the magnetization relaxes into the new direction in the last step of the switching without consuming any additional energy. To switch M back, a higher energy $E(\varphi_2)$ is needed to account for the damping loss in the additional precession by 180° . Each additional switching requires an energy increment $\Delta E_\nu = E(\varphi_\nu) - E(\varphi_{\nu-1})$ to compensate for the damping loss in the ν th large angle precession by 180° . This is a truly ideal situation to measure the dissipation development in large angle precession. The boundaries along which M has switched are contour lines of constant Zeeman excitation energy $E(\varphi_\nu) = \text{const.}$ This is shown in picture 6.2.

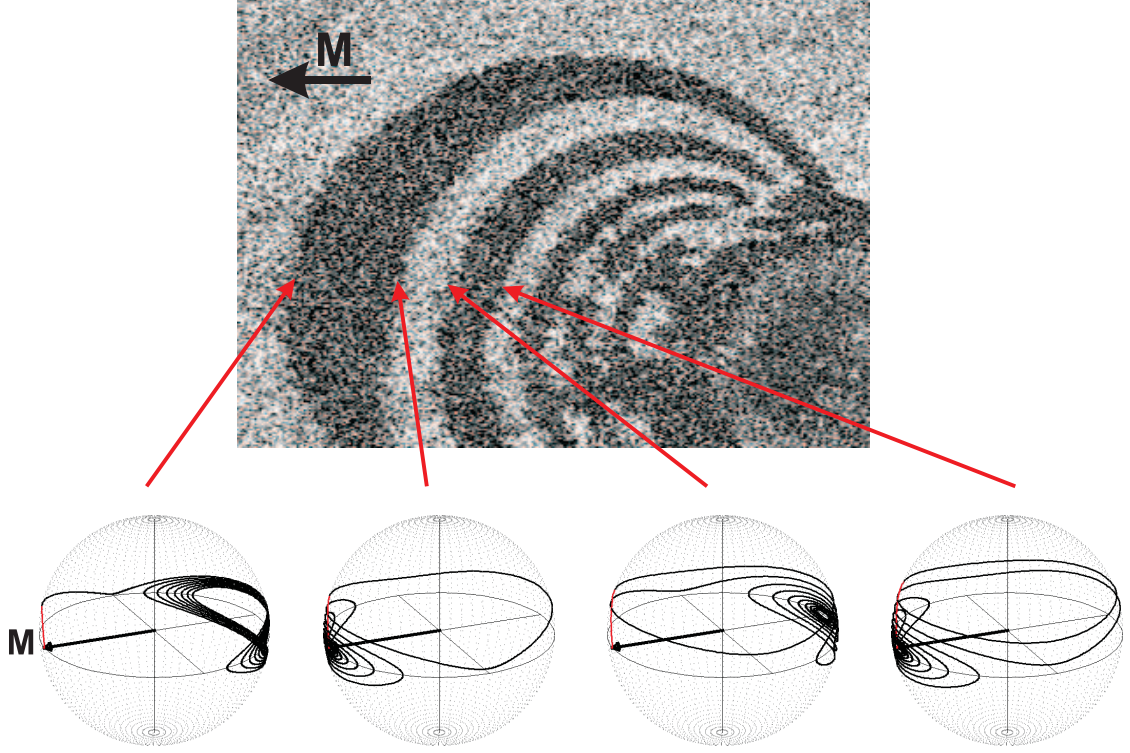


Figure 6.2: Dynamics at the Boundaries in In-plane Media.

The contour lines $E = \text{const}$ for a small damping and very short excitation pulse are calculated from $\varphi \propto x/r^2 = \text{const}$ yielding:

$$\left(\frac{x - a_\nu}{a_\nu}\right)^2 + \left(\frac{y}{a_\nu}\right)^2 = 1 \quad (6.3)$$

The contour lines are thus circles of radius a_ν whose origin is shifted by $\pm a_\nu$ on the x-axis, as shown in figure 6.3.

When the excitation pulse is longer, comparable with the precession time in the anisotropy field, the magnetization not only goes out of the sample plane but also rotates around the easy axis. This has the effect of shifting the whole pattern to one side as shown in figure 6.4.

The validity of (6.3) is proven by figure 6.5 and 6.6 displaying examples of magnetic

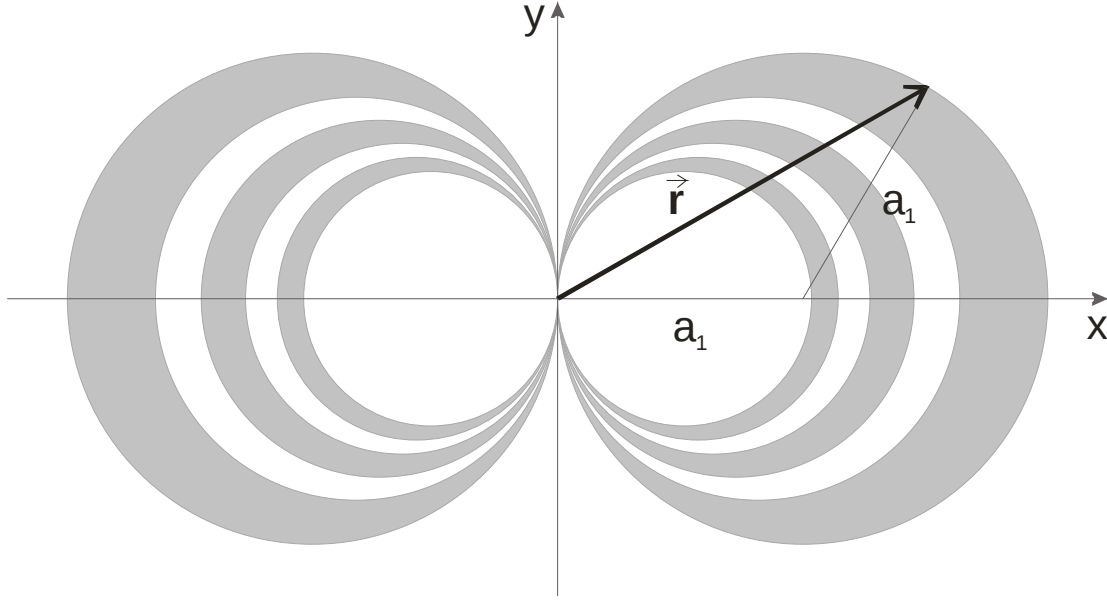


Figure 6.3: Lines of constant excitation for very short magnetic field pulses. Because the torque acting on magnetization is proportional to the sine of the angle between the applied magnetic field and the magnetization, the lines of constant torque (excitation) are circles, which are drawn here for several values of the torque.

switching patterns obtained with ultrathin films premagnetized along the easy direction along the horizontal x-axis. We used single crystalline bcc Fe-films grown epitaxially on a GaAs(001) surface, protected by a capping of 10 ML Au. The films have been characterized by FMR (yielding $g=2.09$), and other techniques [?]. The width of the FMR resonance is found to be independent of film thickness, and increases linearly with FMR-frequency from 9-70 GHz, corresponding to a damping $\alpha = 0.004$. Up to ten switches induced by a single electron bunch can be distinguished, as opposed to at most 4 switches in previous experiments with thicker Co-films [?]. The constants a_ν are obtained by fitting circles (table 6.2) to the patterns as indicated in the figures.

The pattern of figure 6.5 is produced with an electron bunch of charge $Q = 1.73$

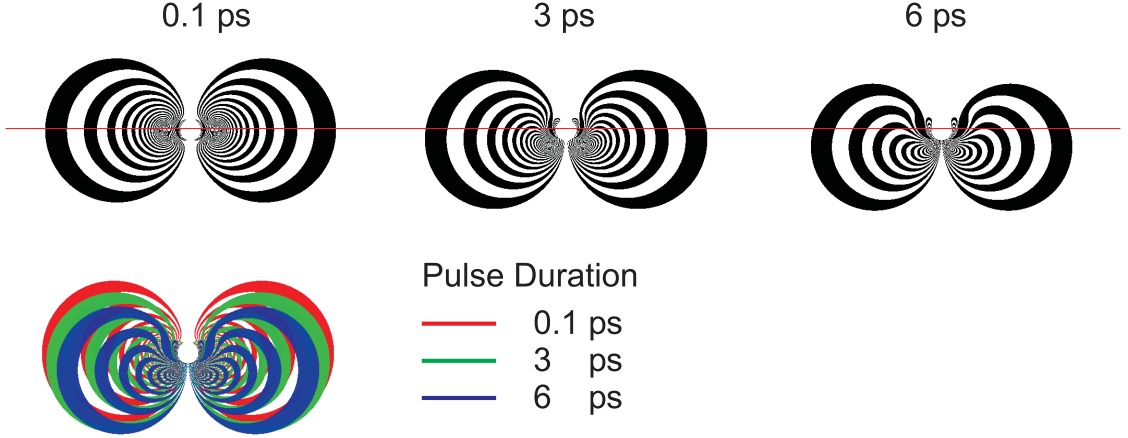


Figure 6.4: Effect of the Pulse Length on the Magnetic Pattern. The red line indicates the center of the electron bunch that passes through the sample. It is also the orientation of the easy axis. As the bunch length gets longer the anisotropy field becomes comparable to the magnetic field created by the bunch and the magnetization rotates also around the easy axis, hence the pattern gets shifted down. One could imagine using this effect to measure the bunch length.

Switching boundary	1	2	3	4	5	6	7	8
Diameter(μm) for 10 ML Fe/GaAs	292	227	200	172	159	139	-	-
Diameter(μm) for 15 ML Fe/GaAs	325	270	238	209	185	167	152	139

Table 6.2: Circle diameters of the switching boundaries for the two samples shown in figures 6.5 and 6.6.

nC in a 15 ML Fe-film with $H_{ani} = 4.72 \times 10^4$ A/m and $H + demag = 128 \times 10^4$ A/m. The pattern of figure 6.6 is generated with $Q = 2.1$ nC in a 10 ML Fe film. The thinner film exhibits a larger uniaxial anisotropy field of $H^{ani} = 8.21 \times 10^4$ but a smaller $H^{demag} = 109 \times 10^4$ A/m compared to the 15 ML Fe-film. The magnetic patterns have been imaged 12 weeks after exposure of the samples to the field pulse by sputtering away the capping layers of 10 ML Au and then imaging the direction of M in spin resolved scanning electron microscopy (Spin-SEM). M is either parallel (light grey) or antiparallel (black) to the horizontal easy direction.

6.3 Potential problems

One type of problem encountered in determining the contour lines 6.3 is due to rugged zig-zag-transitions between regions of opposite M . Such zig-zag domain walls are displayed with high spatial resolution in the bottom section of figure 6.5. The switching leads initially to the unfavorable "head-on" position of M when a contour line runs $\perp$ to the x-axis. As noted before [?], the head on-transitions relax later into the longer, but more favorable zig-zag domain walls. The location of the switching transition is the average over the zig-zag-walls.

A second type of uncertainty arises from the fact that the samples are soft-magnetic with a coercivity of $1 - 2 \text{ kA/m}$ only. This means that domains may easily shift, e.g., in accidental magnetic fields. Apparently, domain wall motions occurred after exposure and deformed the left side of the pattern of figure 6.5 while on the right side, the pattern appears to be undisturbed.

A third problem is the damage caused by the high energy electron bunch in the sample. With the semiconducting GaAs substrate we observe larger damage compared to metallic buffer-layer substrates used in prior experiments [?, ?]. The damage may be attributed to the electric field $E_p = c \times B_p$ running perpendicular the magnetic field B_p of the pulse. E_p is not rapidly screened in a semiconductor, resulting in electrostrictive deformation of the GaAs-template responsible for the uniaxial magnetic anisotropy of the Fe-film. The permanent beam damage is delineated by a halo around the location of beam impact at $r \leq 50 \text{ }\mu\text{m}$. Although the halo is below the distances of the measurable switching events, it cannot be excluded that the magnetic anisotropy is affected transiently even at larger distances by the electrostrictive chock of the template.

With the 10 ML Fe-film, the domain pattern is less regular compared to the 15 ML film. This must be due to larger local variations of the magnetic properties in

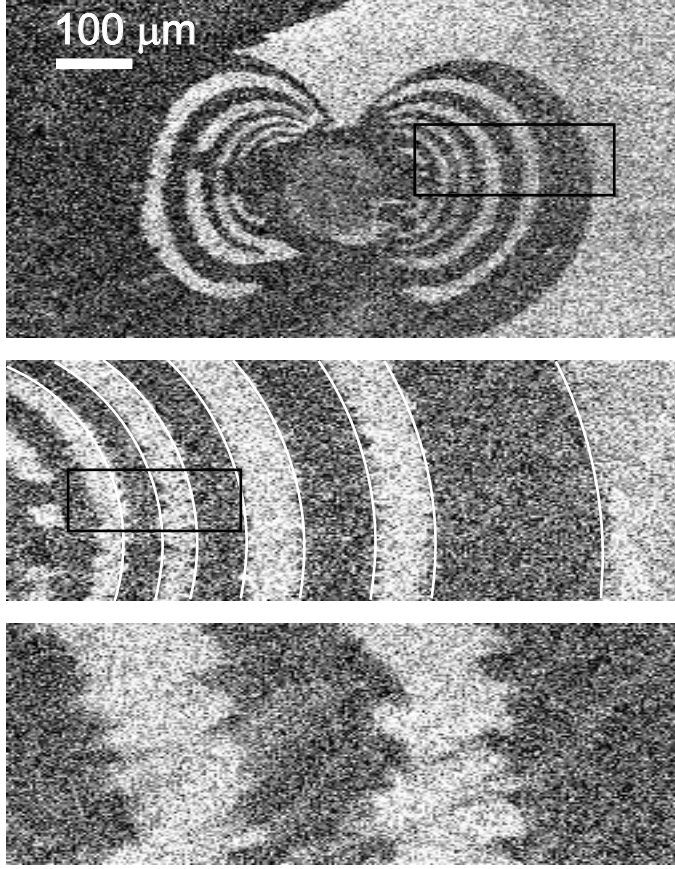


Figure 6.5: Magnetic pattern generated with a single electron bunch in a 15 ML Fe/GaAs(001) epitaxial bcc Fe-film. The magnetic image is obtained by Spin-SEM after sputtering off the capping layer of 10 ML Au. Prior to the field pulse, M is aligned horizontally to the right shown in light grey. The regions where M has switched to the left are shown dark. On the left and lower left side, the pattern is disturbed by motion of domain walls after exposure. In the center, a large spot due to beam damage appears. The framed part is shown at greater magnification in the middle with the fitted circles and at the bottom at still larger magnification exposing zig-zag domain boundaries.

the thinner film at the length scale of $100\ \mu\text{m}$ as the irregularities repeat themselves in different exposures.

6.4 Interpretation of the results

If the energy (6.2) required for the onset of a new switch is plotted in units of K_u vs the angle of precession of M , one obtains the universal switching diagram shown in figure 6.8. The switching diagram is independent of the magnetic parameters of the films, but depends somewhat on film thickness as apparent with increasing

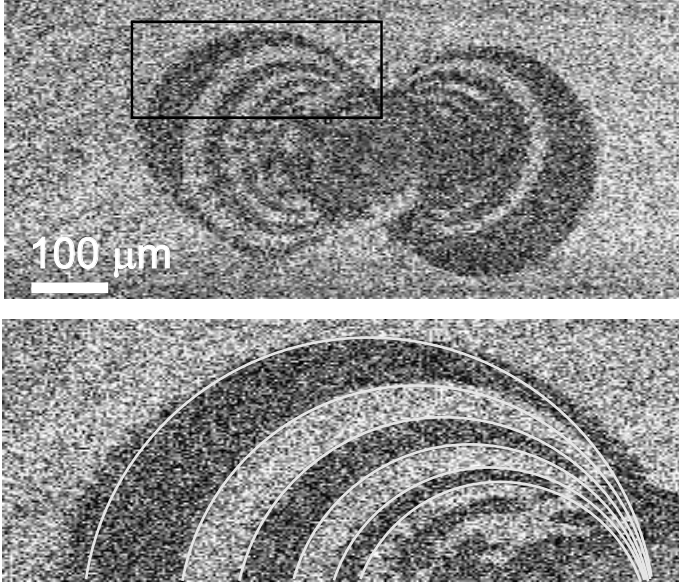


Figure 6.6: Magnetic pattern generated with a single electron bunch in an 10ML Au/10 ML Fe/GaAs(001) epitaxial Fe-film, otherwise like figure 6.5. No after-pulse motion of domain walls occurred in this sample, but the pattern is less regular than with 15 ML

number of switches. The first switch requires the reduced energy $E \approx 1$, compatible with the small damping observed in FMR. The small dissipation contribution in the first precessional switch explains the difficulty to determine it with conventional magnetic field pulses inducing only one switch. Yet already with the second switch, the additional precession by 180° requires much more energy than what results from FMR damping, see figure 6.7. The loss in the higher switches is nearly an order of magnitude larger than the dissipation extracted from FMR.

The increase of the energy loss after the first switch shows that dissipation of spin angular momentum increases with time. Such delayed dissipation is characteristic for the Suhl instability [?], which is the transfer of energy from the uniform precession mode with wavevector $k = 0$ to higher spin wave modes with $k \neq 0$. The transfer of energy, induced by non-linear interactions owing to H_{demag} and H_{ani} , takes time because the numbers of excited non-uniform spin waves grow exponentially with time.

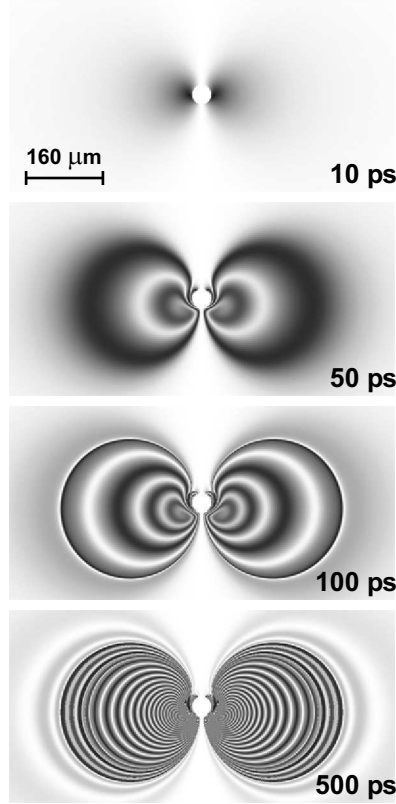


Figure 6.7: Snapshots of the magnetization projection on the anisotropy axis for 10 ML Fe/GaAs sample using the damping measured with FMR. Time and distance scale are indicated, time zero being the time the front of the electron bunch enters the sample. Initially the sample is uniformly magnetized (white) in one direction along the anisotropy axis. The gray scale indicates the projection on that axis, white being the initial direction and black the opposite. Although the intermediate snapshots look similar to picture in figure 6.6 the last snapshot at 500 ps (close to the end of the relaxation) has many rings not appearing in the experimental image. Some other additional damping prevents the sample to relax into the pattern shown in the last snapshot.

A quantitative theory for the dissipation caused by the Suhl instability has been developed recently [?]. In the inset of figure 6.8 we show simulations for an area of $1 \mu\text{m} \times 1 \mu\text{m}$ of the 10 and 15 ML Fe-film with a respective pulse amplitude that completes the first switch. It demonstrates one important consequence of the generation of higher spin wave modes, namely the decrease of the space averaged order parameter M/M_s with time. It is seen that M/M_s decreases sharply $\approx 50 \text{ ps}$ after the field pulse, and recovers slowly through spin lattice relaxation of the spin waves. Now, from the time t_ν after the field pulse at which the last change of sign of M_x occurs, we know the moment in time at which the energy consuming part of the switch ν is terminated. With 15 ML-Fe we obtained $t_1, \dots, t_8 = 40, 115, 155, 195, 235, 270, 310, 360 \text{ ps}$ respectively. Large dissipation is observed only *after* the first switch. This agrees with the 50 ps delay seen in the development of spinwave scattering.

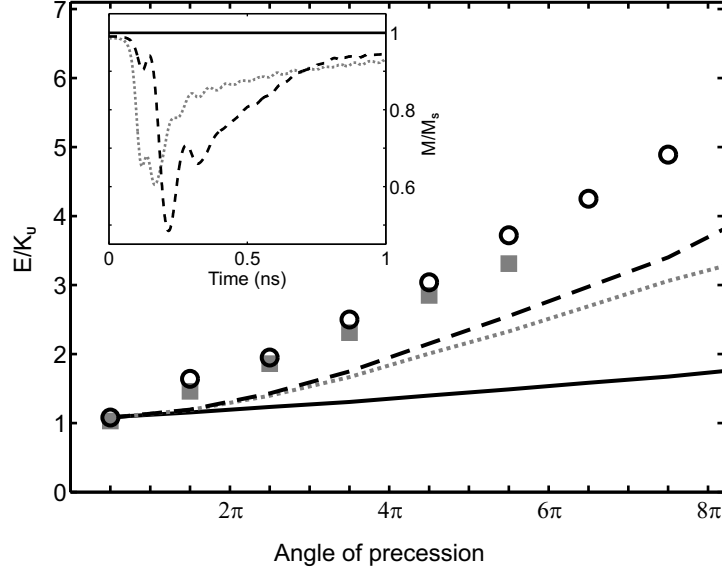


Figure 6.8: Energy deposited in the spin system in units of the uniaxial in-plane anisotropy constant K_u vs polar precession angle. Data points are for 10 Fe-ML(squares) and 15 Fe-ML(circles). The simulations are with the FMR Gilbert damping $\alpha = 0.004$ and no magnon scattering (—), and for 10 Fe-ML ($\cdots$) and 15 Fe-ML (--) including magnon scattering. The inset shows the relative saturation magnetization $M(t)/M_s(0)$ where t is the time after an exciting field pulse of amplitude 0.24×10^6 A/m for 10 Fe-ML ($\cdots$) and 0.175×10^6 A/m for 15 Fe-ML (--). But without magnon scattering(—), $M(t)/M_s = 1$

Furthermore, the fluctuations of M/M_s in time and space manifest themselves through increasingly random switching as the angle of precession grows. Another characteristic of the Suhl instability concerns the film thickness. To conserve energy and momentum, the effective scattering of the uniform mode requires the excitation of low energy spin waves. The phase space for such low energy, long wavelength modes decreases with film thickness, and this explains the experiment as well as the simulation both showing smaller dissipation as the number of ML is reduced. Hence there is no reasonable doubt that the Suhl instability contributes significantly to the dissipation observed in the experiment.

However, as apparent from figure 6.8, the simulations are short by a factor 2 to fully account for the observed damping. Surface roughness is known to contribute

to the damping α . However, the detailed analysis based on [?] shows that the surface roughness measured on the present films [?] is not enough to explain the observations, and furthermore should show up in FMR as well. We therefore have to conclude that additional, so far unknown relaxation mechanisms must be active in large angle precession of the magnetization as well.

Chapter 7

Experiments with Perpendicular Magnetic Media

7.1 Introduction

The dynamic response of a spin system reveals itself in the image of the final magnetic switching pattern generated by very short, intense and gaussian shaped magnetic field pulses. Our experiment shows that under these extreme conditions, precessional switching in magnetic media supporting high bit densities no longer takes place at well-defined field strengths; instead, switching occurs randomly within a wide range of magnetic fields. We attribute this behavior to a momentary collapse of the ferromagnetic order of the spins under the load of the short and high-field pulse.

7.2 Experimental details

The experiment is based on the unique magnetic field pulses generated in solids by a passing-through finely focused high energy electron bunch as shown previously in chapter 2. The magnetic field lines are the circular field lines generated by a

Property	Value
Energy of electrons	28 GeV
Number of electrons	$(1.05 \pm 0.05) \times 10^{10}$
Cross section (gaussian profile with $\sigma_x \times \sigma_y$)	$10.8 \times 7.4 \mu m$
Pulse length (gaussian profile with σ_z)	0.7 mm
Pulse duration ($\sigma_t = \sigma_z/c$)	$2.3 \times 10^{-10} s$
Peak magnetic field $B_p(Tesla)$ at distance $R(\mu m)$	$B_p = 54.7/R$

Table 7.1: Some characteristics of the electron beam used in the experiment.

straight electric current. The peak field strength is calculated from Ampères law valid for distances greater than the size of the beam. A summary of the electron beam characteristics is shown in table 7.1. The electron beam has a gaussian density profile in all three directions and we use the notation B_p for its peak magnetic field intensity.

With the films magnetized perpendicular to the film plane, the magnetic field B and magnetization M are orthogonal everywhere. This is the optimum geometry to induce a precessional motion of M about the magnetic field.

Once M has precessed about B by an angle large enough to cross the magnetically hard plane of the sample, it will continue to relax (spiral) by itself into the opposite direction. In the end it has switched from one easy direction into the opposite easy direction. If the magnetic field terminates before M has reached the hard plane, M is expected to relax back to its original perpendicular direction, hence no switch is observed. The condition for switching is that the angle of precession $\varphi \geq \pi/2$, where $\varphi \propto B_p \sigma_t$, σ_t describing the gaussian temporal profile of the beam. We thus obtain the switching condition $B_p \sigma_t \geq const.$

For our case of uniaxial perpendicular magnetocrystalline anisotropy, no demagnetization field is generated that could continue to provide a torque propelling M uphill over the hard plane, both demagnetization and anisotropy fields having the same direction. This is different with uniaxial in-plane magnetized materials where

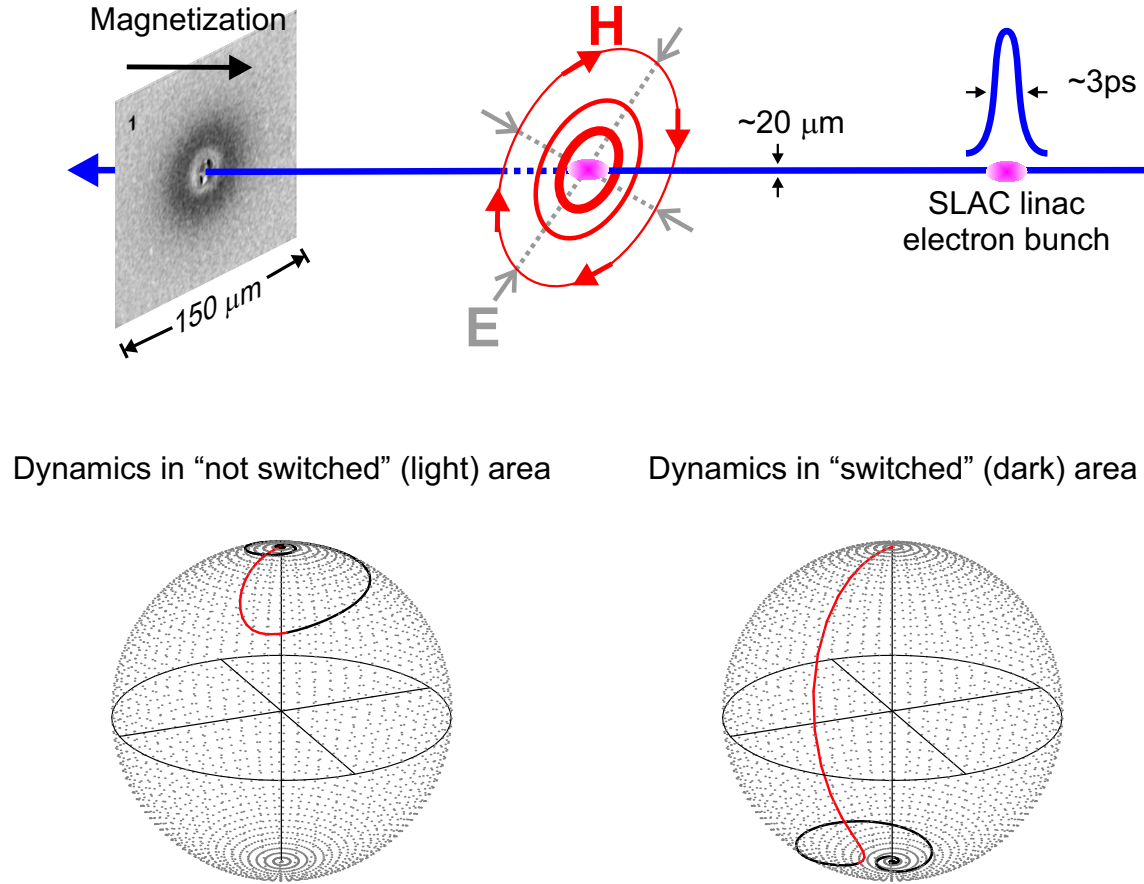


Figure 7.1: An illustration of the experiment with the dynamical path of the magnetization for two locations on the sample with different magnetization switching results. Outer areas that are light-colored are not exposed to field of enough intensity to switch them, whereas the dark areas precess during the field pulse (red color) over the magnetically hard plane (the equator), which is also the sample plane. North and south pole are the equilibrium directions of the magnetization.

the field pulse causes M to precess out of the plane of the film and a demagnetization field along the surface normal is generated, resulting in demagnetization being perpendicular to the anisotropy field. Precession about this demagnetization field can lead to multiple in-plane reversals of M after the field pulse has ceased to exist [?]. Therefore, perpendicular magnetized materials are unique in providing the opportunity to observe any fields different from the anisotropy field that might have been

generated by the interaction of the spins with the field pulse.

Generally, precessional magnetization switching is interesting because it is faster by an order of magnitude and uses much less energy to reverse the magnetization $\vec{M}$ compared to the traditional methods of switching in use today [?, ?, ?]. Furthermore, $\vec{M}$ may be switched “back” (by rotating another 180° in the same direction) without changing the polarity of the magnetic field pulse simply by applying the switching pulse again. This characteristic is used here to test the reversibility of the switching by applying identical pulses several times. If the switching is deterministic, the second pulse should restore the magnetic state present before the first pulse, and so on. All patterns produced by an odd number of pulses should be identical and so should be all even pulse patterns. In contrast, we show here that the switching probability is independent of whether or not a particle has switched before and is therefore dominated by a stochastic process. As a consequence, only the average motion of $\vec{M}$ can be described by the conventional coherent precession model. This remained hidden in previous work [?] where reversibility was not tested.

To test this switching, films of perpendicular granular magnetic recording media of the CoCrPt-type developed for high-density magnetic recording [?] were used. The main condition for high-density recording is that the grains are decoupled so that the medium can sustain narrow transitions between “up” and “down” bits. The decoupling of the grains occurs through segregation of Cr to the grain boundaries induced by deposition at elevated temperature. The grain size was determined by X-ray diffraction to be $20 \pm 5 \text{ nm}$, while the film thickness was 14 nm . This grain size is so small that the magnetic field is homogeneous over the grain size to better than 0.1%. We can then assume that the switching of a grain occurs in a homogeneous applied field. The films were protected from atmospheric corrosion by a cover of 1.5 nm Pt and used glass substrate with appropriate thin buffer layers, with and without adding a soft magnetic underlayer such as needed in perpendicular recording

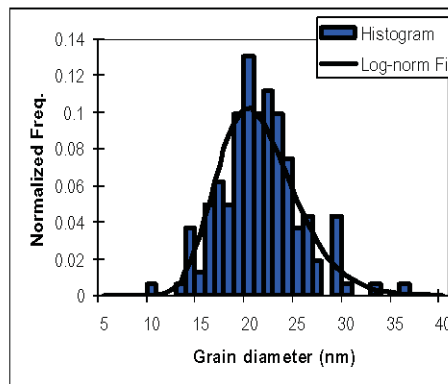


Figure 7.2: Grain size distribution of perpendicular granular magnetic recording media as determined by X-ray diffraction for sample *CoCrPt I* in table 7.2

[?].

7.3 Magnetic Patterns

Before exposure, the samples were magnetized perpendicular to the film plane into what we shall call the "up" direction. We recorded patterns on the same sample corresponding to a single shot (pulse), a pattern corresponding to two shots at the same location, and so on, up to seven consecutive shots per pattern. The time separation of consecutive shots was 1 s. Three weeks after exposure, the perpendicular component of M was imaged by polar magneto-optic Kerr microscopy. A set of such images is shown in figure 7.3. The spatial resolution of Kerr microscopy is $1\ \mu m$, so that we integrate over $\approx 2,500$ grains. The spot in the center of the pattern is due to beam damage. It extends to roughly twice the beam focus. The increase of the damaged area with the number of shots is due to beam jitter, which is estimated to be $\pm 2\ \mu m$ per shot only. The grey scale of the images is such that the light regions near the edge of the frames correspond to the initial "up" state. Darkening indicates

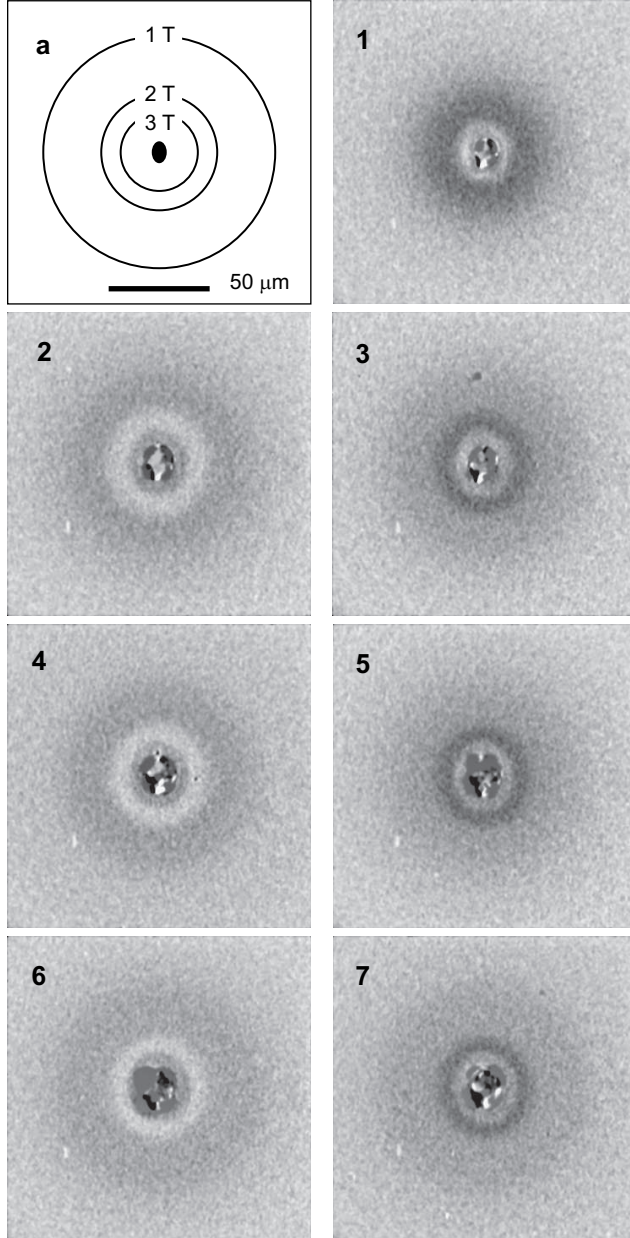


Figure 7.3: Magneto-optic patterns of magnetization for *CoCrPt I* in table 7.2. Diagram at top left shows contour lines of constant peak magnetic field B_p with area of the electron beam focus in the center around which there is localized beam damage. The numbers on subsequent panels indicate the number of electron bunches (shots) that passed through the sample. Grey contrast is such that the outer light region corresponds to M in the initial "up" state. As darkening intensifies, M has switched increasingly to the "down" direction. The contrast in the central region at $R < 10 \mu m$ is due to beam damage.

that particles in the regions have increasingly switched to the "down" direction.

It is evident that switching occurs along circular contour lines $B_p = const$, with the contrast changing gradually over a distance of tens of μm , rather than abruptly. The switching is not reversible, because the second pulse does not return M to the

initial "up" direction. For odd shot numbers, the dark ring where M has switched from "up" to "down" narrows with increasing number of shots, whereas the outer grey zone corresponding to partially switched M expands. With an increasing number of even shots, the central light ring narrows and the outer grey zone expands. This switching behavior is characteristic of a stochastic process. Starting with a homogeneous magnetic "up" state, it takes only seven shots to create a random distribution of magnetization directions throughout the large grey zone, where M is "up" in some grains but "down" in others.

7.4 Interpretation of the results

To describe the stochastic switching, consider that the angle φ of precession could be short of $\pi/2$ needed for switching. The lacking precessional angle may be supplied by random torques or by random initial conditions. If we assume that the probability p of such stochastic events is gaussian and can be expressed as the probability density of an additional magnetic field Γ :

$$p(\Gamma) = \frac{1}{\Delta B \sqrt{2\pi}} e^{-\frac{\Gamma^2}{2(\Delta B)^2}} \quad (7.1)$$

The relative magnetization M (the magnetic order parameter) then depends on the pulse peak amplitude B_p and is given by the fraction of particles that switch minus the fraction of particles that do not switch:

$$M(B_p) = \int_{-\infty}^{B_1 - B_p} p(\Gamma) d\Gamma - \int_{B_1 - B_p}^{+\infty} p(\Gamma) d\Gamma \quad (7.2)$$

By choosing the average switching pulse amplitude $B_1 = 1.70 \text{ T}$ and its variance $\Delta B = 0.59 \text{ T}$ we obtain the order parameter $M_1(B_p)$ after the first shot generated

from the uniform initial state $M_0 = +1$. Substituting the variable B_p by R yields the radial dependence $M_1(R)$ of the magnetization after the first shot. $M_1(R)$ is plotted for $R > 20 \mu m$ as a solid line on top of the data points in panel 1 of figure 7.4. It agrees with the experimental data. The increase of the observed $M_1(R)$ at $R < 20 \mu m$ indicates the onset of the second switch where M precessed by $\varphi \geq 3\pi/2$. We do not analyze this second switch because it occurs close to the beam damage area. The easy axis dispersion has been determined with X-ray diffraction to be 5.5° (full width half maximum). This generates a distribution of switching fields which is much smaller than ΔB .

The other distributions of $M_n(R)$ shown as solid lines in panels 2 – 6 of figure 7.4 are generated by multiplication $M_n(R) = M_{n-1}(R) \times M_1(R) = M_1^n(R)$. This accounts very well for the features observed in the experimental data shown as points, despite the fact that raising $M_1(R)$ to the n -th power enhances errors. Experimental errors are caused by beam jitter, variations in the number of electrons per bunch, and the uncertainty in the extrapolation of $M_1(R) \rightarrow +1$. At any rate, multiplicative probabilities are the signature of a random variable. Therefore, this analysis reveals that a memoryless process, usually referred to as a Markov uniform stochastic process, dominates the switching.

Different samples have been studied within a range of magnetic parameters such as saturation magnetization and magnetic anisotropy. Information is also available [?, ?] about switching with older media types such as *Co/Pt* magnetic multilayers and *CoPt* alloys, designed for thermomagnetic recording and exhibiting exchange coupled grains and larger anisotropy. The relative broadening $\Delta B/B_o$ of the first switching transition has been found to be of similar magnitude than observed here with the largely uncoupled grains of *CoCrPt*. The conclusion emerging from all experiments is that stochastic switching is a general feature of ultrafast precessional magnetization reversal. The results of the experiments are presented in the table 7.2.

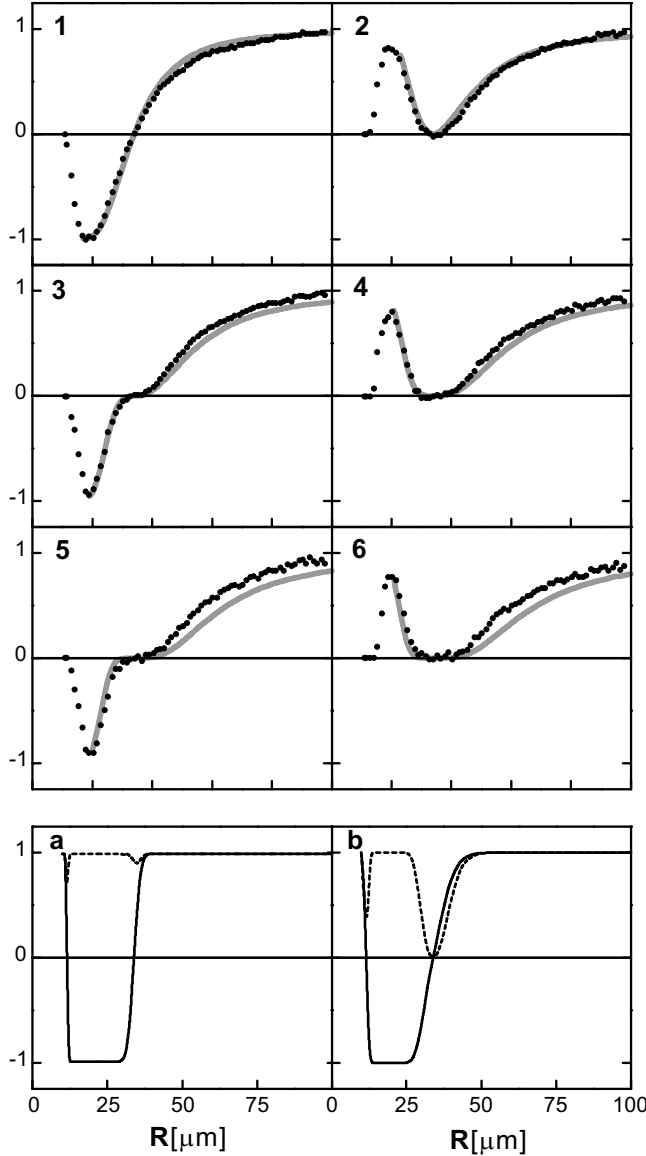


Figure 7.4: Magnetization (order parameter) radial profile $M_n(R)$ for figure 7.3. [a] Data points are from averaged radial cuts of the Kerr images of figure 7.3, setting $M(100 \mu\text{m}) = +1$ and $M(20 \mu\text{m}) = -1$. The grey lines are generated from $M_n(R) = M_1^n(R)$. [b] Calculated $M_1(R)$ (—) and $M_2(R)$ (---) with the observed easy-axis dispersion of 5.5° [?], showing $M_2(R) \simeq M_0 = +1$ in gross contradiction to the experiment. [c] Calculated $M_1(R)$ (—) and $M_2(R)$ (---) assuming the excitation of the uniform precession mode (figure) corresponding to $K_u V/kT = 40$ (anisotropy/thermal energy ratio), where K_u is the uniaxial crystalline anisotropy constant, V the volume of a grain, k the Boltzmann factor and T the temperature [?].

The magnetic signal obtained by Kerr microscopy for samples *CoPtCr I – II* is shown in figure 7.5. With samples *CoPt(95)* and *Co/Pt(98)* the magneto-optic patterns are not of sufficient quality to permit similar quantitative analysis. The earlier patterns are asymmetric due to oblique illumination, unspecified magneto-optic contrast enhancement, and moreover, the contour lines of constant magnetic field

MediaType	M_s (T)	H_c (kA/m)	H_{eff} (kA/m)	Dispersion of easy axis(°)	GrainSize (nm)	B_0 (T)	ΔB (T)	$2\Delta B/B_0$
CoCrPt I alloy	0.65	483	684	5.5	20.6 ± 4	1.7	0.59	0.7
CoCrPt II alloy	0.58	171	398	11	19.9 ± 5.1	1.55	0.57	0.74
CoCrPt II alloy on soft underlayer	0.58	203	398	12.7	19.9 ± 5.1	1.55	0.51	0.66
CoPt(95) alloy[?]	0.47 – 0.58	117 – 178	1380 – 1600	≈ 0	-	-	-	0.6
CoPt(98) multilayers[?]	-	-	1274 – 2548	0 – 20	15	-	-	0.2 – 0.8

M_s - saturation magnetization; H_c - coercive field; H_{eff} - effective anisotropy field

B_0 - average switching field; ΔB - variance of switching field

$2\Delta B/B_0$ - relative width in switching fields

SUL - soft magnetic underlayer (*FeCoB*), see figure 7.6

Table 7.2: Some older and present results of running the electron beam through different magnetic media. In all cases the relative transition width is similar

were quite elliptical. The difference in figure 7.5 between samples *CoCrPt I* and *CoCrPt II* may be accounted for by the difference in the values of the anisotropy. It should be noted, that the magnetic anisotropy has a reduced influence in precessional reversal. Increasing it by a factor of 1.72 on going from *CoCrPt II* to *CoCrPt I* increases the average switching pulse amplitude by a factor of 1.10 only. In the hysteretic switching commonly practiced one expects that the switching field is proportional to the anisotropy.

The soft-magnetic underlayer(SUL) is needed in perpendicular media to enhance the perpendicular field of the writing head pole. This happens by inducing an image magnetic pole in the underlayer. Without SUL, there is no high-density perpendicular magnetic recording. The magnetization also interacts with its own induced magnetic image in the soft magnetic underlayer (see figure 7.6), yet this additional magneto-static interaction does not have a significant effect on the width of the transition. The curves in figure 7.5 for the sample *CoCrPt II* with and without SUL are nearly identical, confirming the theoretical conjecture that magnetostatic interactions are not responsible for the transition width.

The angular velocity of magnetization precession is independent of grain size and it is proportional to the effective magnetic field at the grain location. If all grains precess

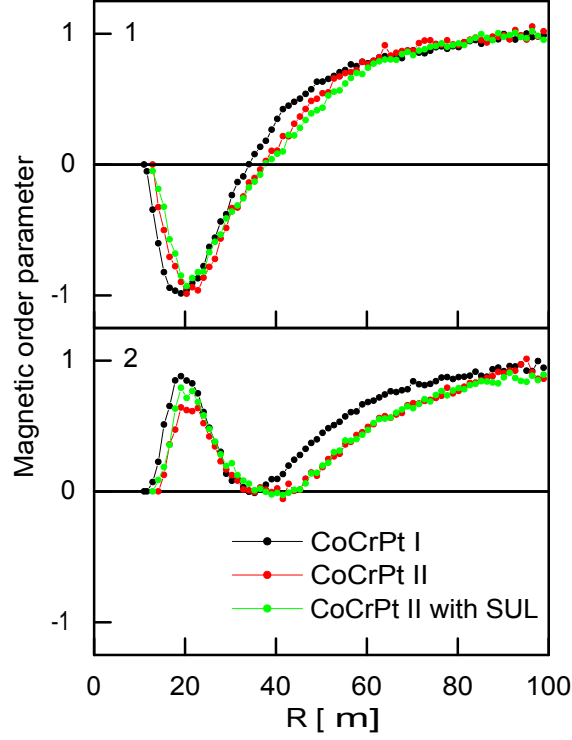


Figure 7.5: Radial profile of one and two shot locations for different types of samples.

with the same angular velocity, they will arrive at the hard plane simultaneously and the dipolar coupling field vanishes just at the critical moment in time. The mean path followed by the magnetization, calculated from the Landau-Lifshitz-Gilbert equation assuming a damping parameter of the precession equal to 0.3, is shown in figure 7.7.

To explore causes of the randomness, we carried out various calculations using the Landau-Lifshitz-Gilbert equation, introduced in chapter 5. Theoretical results that explore two hypothetical sources of the randomness are shown in figure 7.4. Panel **b.** demonstrates that static dispersion of the easy axis of magnetization in the decoupled grains cannot produce anything but deterministic switching reversing M to the original state $M_0 = +1$ in the second shot. This is in gross contradiction to the

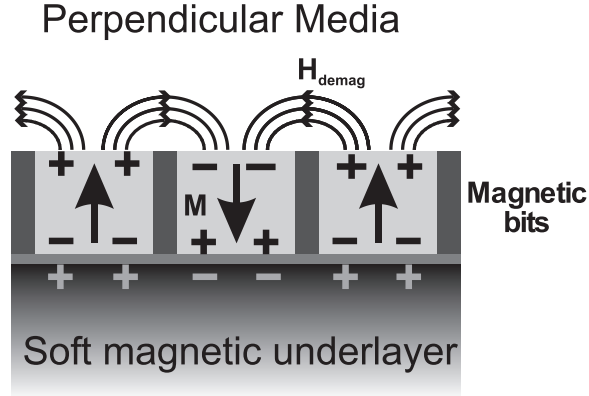


Figure 7.6: Illustration of the role of soft magnetic underlayer in perpendicular media. Magnetization (M) interacts with its image in the soft magnetic underlayer increasing the magnetostatic interaction of the grains by a factor of about two.

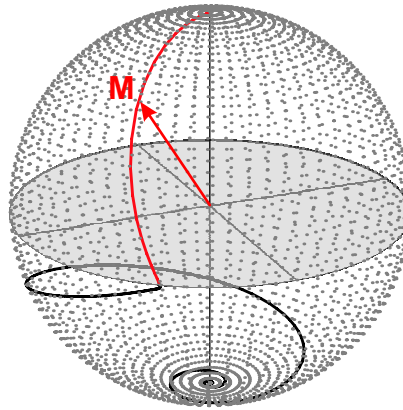


Figure 7.7: The mean path followed by the magnetization with a pulse amplitude B_p close to B_0 . The portion in red represents the pathway during the magnetic field pulse.

experiment. Panel **c.** explores thermal excitations in terms of the uniform precession mode (illustrated in figure 7.9). The degree to which the uniform mode is excited is known from the long-term stability of the magnetic bits [?]. It induces randomness in the direction of M before the arrival of the field pulse and indeed generates dispersion of $M(R)$, but the dispersion is much too small to explain the data.

The grain size distribution is important for thermal fluctuations of the magnetization direction. The amplitude of such fluctuations depends on the ratio between anisotropy energy and thermal energy $K_u V / kT$ (K_u is the anisotropy energy density

and V is the volume of the grain). All our samples have similar grain size distribution and figure 7.2 shows it for *CoCrPtI* sample.

The effect of heating of the sample by the electron pulse can be asserted without calculation. The supersonic heat wave emerging from the point of beam impact requires 10^{-9} s to travel $1 \mu m$. However, the switching at $R > 20 \mu m$ is already completed at that time. Similarly, magneto-static coupling between the grains cannot explain the variance of the switching fields because it is small at the end of the field pulse when the spins have precessed close to the hard plane.

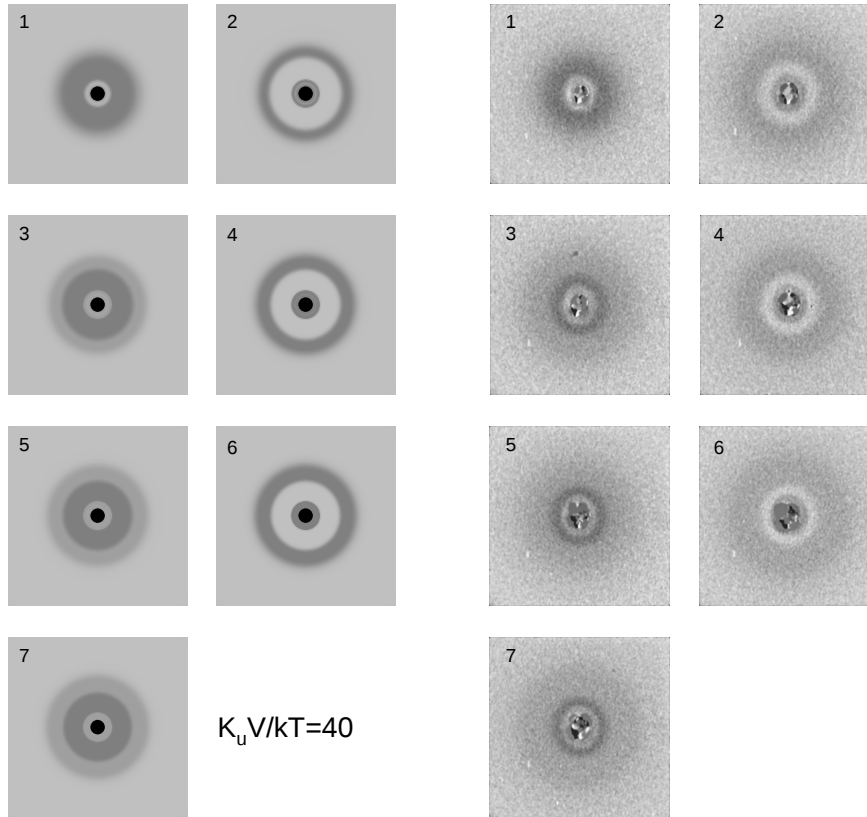


Figure 7.8: Transition broadening due to thermal fluctuation for $K_u V/kT = 40$. The left side shows the simulation and the right side the experimental images.

The thermally activated homogeneous precession mode generates deviations of $\vec{M}$

from the ideal initial direction. Using the resulting variable initial conditions prior to the arrival of the pulse one can explain the width of the switching transition by assuming $K_u V/kT = 8$. Such particles would be super-paramagnetic [?]. Yet the media are evidently not super-paramagnetic, because they have retained the patterns written by the electron bunches for three weeks, and in fact were designed to carry magnetic information for years. Therefore, the thermal fluctuations prior to the arrival of the field pulse cannot be the main reason for the broadening of the switching transition. The broadening due to thermal fluctuations for a $K_u V/kT = 40$, a value close to the lower limit for stability of the information stored, is illustrated in figure 7.8.

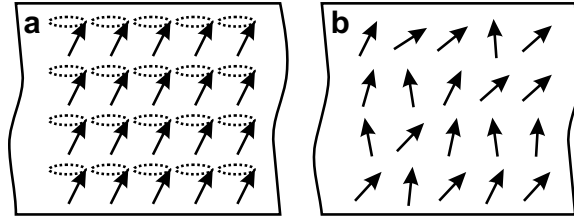


Figure 7.9: Spin motion in a magnetic grain. [a] The uniform precession mode of the spins with wave-vector $q = 0$. The excitation of this mode determines the long-term stability of the magnetization direction in the grain [?]. [b] A moment in time with non-uniform excitation of the spins. At ambient temperature, these excitations have small amplitude, which however dramatically increases after the field pulse has been applied. Sizeable exchange fields are generated by the angles between neighboring spins that can account for the random torques operating after the magnetic field pulse.

The thermal fluctuations within a grain also include higher modes in which the spins are not parallel to each other (illustrated in figure 7.9). At ambient temperature, these fluctuations have small amplitude. Calculations show that the sharply rising field pulse greatly amplifies the pre-existing thermal randomness. The amplification of the thermal fluctuations leads to the observed variance of the switching fields.

The crystalline magnetic anisotropy field $H_A = 1.2 \times 10^6$ A/m, the saturation

magnetization $M_s = 0.652 T$, and the average switching field $B_1 = 1.7 T$ are compatible with the Landau-Lifshitz-Gilbert equation if the damping of the magnetization precession in a grain is assumed to be $\alpha = 0.3$. This extremely large damping shows that torque is lost at a high rate to the spin system, proving indeed the excitation of spin fluctuations. It is well known that the spin system is pushed easily into auto-oscillation and chaos as the absorbed power increases [?, ?]. At the end of the field pulse, the non-equilibrium modes illustrated in figure 7.9 exert the postulated random torques. Our experiment reveals a "fracture of the magnetization" under the load of the fast and high field pulses, putting an end to deterministic switching at shorter time scales.

7.5 In-plane magnetic media

Beside the perpendicular media, in-plane media were also studied, although lately the magnetic recording industry moves to perpendicular magnetized media as it enables a denser packing of bits per surface area.

The magnetic anisotropy of the in-plane media has to be quite large to preserve the orientation of the bit against the thermal fluctuations over a long period of time. The saturation magnetization is just large enough to give a readable magnetic field at the magnetic transition, see fig 7.10. Since the magnetic thermal stability is given by the volume of the magnetic bit, one can enhance it by antiferromagnetically coupling an underlayer that doesn't contribute to readable signal. This is a so called synthetic antiferromagnet (SAF).

We run the same electron beam, see table 7.1, through our samples and saw patterns that looks like the one in figure 7.11. Samples with different thickness for the antiferromagnetically coupled underlayer were used but no significant difference was observed as shown in the line scans in figure 7.12. The main reason is that the

Synthetic Antiferromagnet

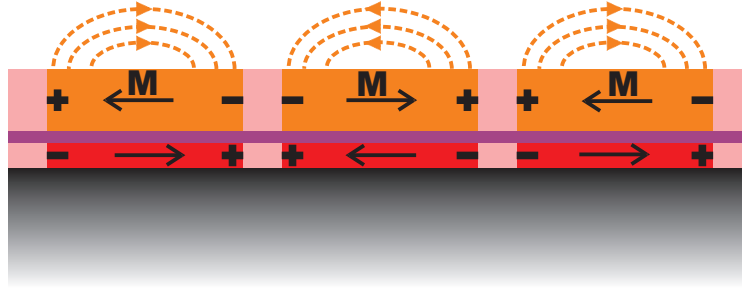


Figure 7.10: The principle of synthetic antiferromagnet underlies most of the in-plane magnetic recording media. Two magnetic layers are antiferromagnetically coupled by a very thin nonmagnetic metallic layer, usually Ru. The stray magnetic field of the transition between domains at the surface is not significantly changed but the thermal stability of the whole structure is enhanced.

two layers precess in unison and no additional demagnetizing field is generated. Thus one can use the macrospin approximation to explain reasonably well the shape and size of the pattern.

A simulation using the macrospin approximation is shown in figure 7.13, where the in-plane uniaxial anisotropy field is $H_{anis} = 0.89 \times 10^6 \text{ A/m}$, the demagnetizing field is $H_{demag} = 0.33 \times 10^6 \text{ A/m}$ and a damping of $\alpha = 0.01$ is used. The magnetic material usually has a random anisotropy direction as sputtered on the magnetic disk but these samples have a preferential distribution along the circular direction on the disk to enhance the magnetic signal. If all magnetic grains had the same orientation of the easy axis one would see details inside the magnetic pattern, however, because of the random distribution the pattern becomes diffuse.

A comparison with the in-plane magnetic thin films reveals that, for the magnetic recording media, the out of plane demagnetization energy is much less than the uniaxial in-plane anisotropy energy ($H_{anis} = 0.89 \times 10^6 \text{ A/m} < H_{demag} = 0.33 \times 10^6 \text{ A/m}$). The applied magnetic field cannot store much energy by bringing the magnetization out of the sample plane and the dynamics looks very much like a

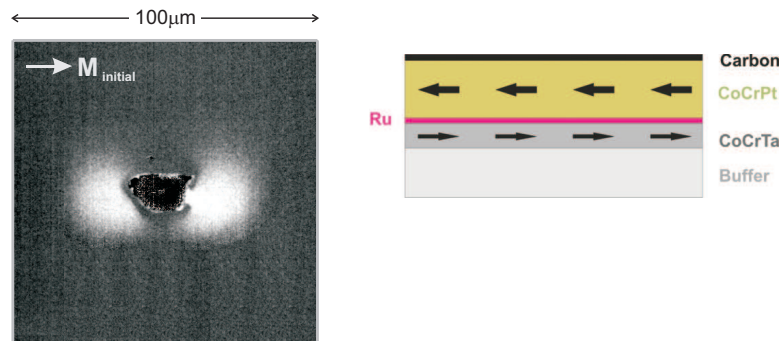


Figure 7.11: A typical magnetic pattern for in-plane media with the usual chemical composition of the layers. An initially premagnetized sample is exposed to the circular magnetic field of the electron beam. The beam damage can be seen as the dark area in the middle of the left picture. The picture was taken with Photo-Electron Emission Microscopy (PEEM) using circularly polarized x-rays in order to be sensitive to the magnetic signal.

swing from one direction to the opposite as shown in figure for a point situated $20 \mu m$ from the electron beam center.

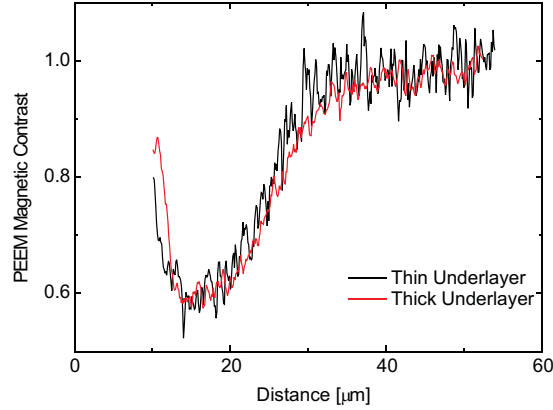


Figure 7.12: Line scans for different thickness of the underlayer in the in-plane magnetic media. In the precessional switching the underlayer has the same motion of the magnetization as the overlayer and does not contribute any additional demagnetization field.

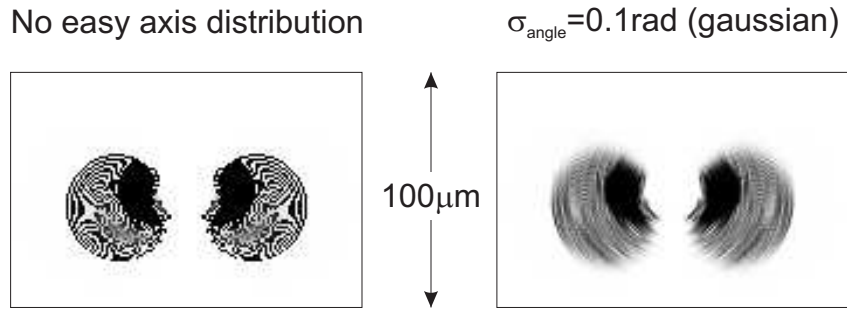


Figure 7.13: In-plane media simulation of the magnetic pattern using the macrospin approximation. The left picture shows the pattern when all grains have the same easy axis direction, while on the right the average over a gaussian distribution of the direction is taken.

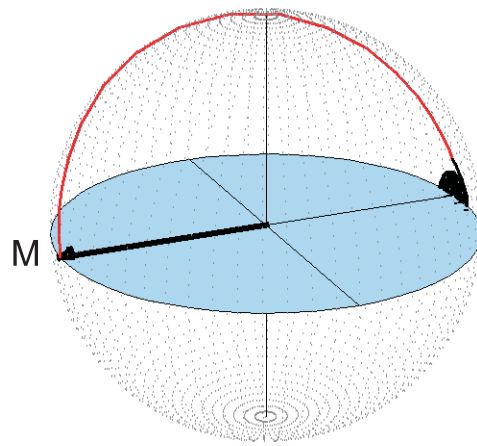


Figure 7.14: Magnetization dynamics for a point $20\mu m$ from the beam center. The applied field makes the magnetization precess across the hard plane from the initial easy direction (red curve). The demagnetizing energy as the magnetization is brought out of the sample (equatorial) plane is small and not effective in storing energy from the applied field.

Chapter 8

Conclusions

This thesis describes new results in precessional dynamics of the magnetic materials using the magnetic field pulse associated with an electron bunch from a linear accelerator. The dynamics was inferred from the shape and size of the magnetic pattern imprinted on the initially uniformly magnetized sample. Although we don't have real time information as that obtained in pump-probe experiments, each location on the pattern sees a different applied field and we get a good statistics not easily obtained in pump-probe experiments. Additionally, the precession of the magnetization around the demagnetization field of the in-plane samples provides a stopwatch for the switching boundaries.

The perpendicular magnetic media patterns can be explained if we assume a random magnetic field in addition to the usual one caused by the thermal fluctuations. This field might come from the energy stored in the exchange interaction between the spins. The samples show enhanced damping of the uniform precession mode, consistent with the above hypothesis. A parallel can be made with ferromagnetic resonance where high power rf excitation leads to chaotic dynamics. The Fourier transform of our magnetic field pulse does contain large amplitude, high frequency components. The additional randomness found in our experiment could impose limitations on the

reliability of magnetic switching at very high speed if the magnetic recording industry will be able to go from around 1 ns to about 10 ps bit writing time.

The model thin magnetic films developed big patterns with many rings due to the low in-plane uniaxial anisotropy. The position of the switching boundaries tell how much energy is needed to push the magnetization over the anisotropy barrier to the other direction. By subtracting this from the energy pumped by the magnetic field of the pulse we get the energy dissipated by the system. A peculiar feature of the pattern is that the first outside ring is thicker than the inner ones. A micromagnetics simulation shows that the spin wave scattering of the uniform mode into higher modes. This takes time to develop and the it is not active for the first switching boundary. The additional dissipation due to this mechanism is still not sufficient (by a factor of two) to explain location of the rings. Here again there might be some additional mechanism for dissipation of angular momentum and energy.

Two main features of the magnetic field pulses are important to be simultaneously present for meaningful precessional switching experiments: high intensity and short duration. The tabletop experiments parameters, although improving, are still a factor of 10 behind in either of them and a factor of 100 combined. Thus they are limited to study of soft magnetic materials. On the other hand accelerator electron bunches of 100fs duration are currently available and experiments exploring this time scale are scheduled to be run shortly after the submission of this thesis. A preliminary test experiment showed a chaotic magnetic pattern and perhaps unexpected results will come out.

Appendix A

Liénard-Wiechert Potentials

A.1 Charge in uniform motion

Instead of describing the electromagnetic field by $\mathbf{E}, \mathbf{B}$ we'll describe it by the scalar potential ϕ and vector potential $\mathbf{A}$, a totally equivalent approach, with

$$\mathbf{E} = -\nabla\phi - \frac{\partial\mathbf{A}}{\partial t} \quad , \quad \mathbf{B} = \nabla \times \mathbf{A} \quad (\text{A.1})$$

In free space and using the Lorentz gauge condition $\nabla \cdot \mathbf{A} + \frac{1}{c^2} \frac{\partial\phi}{\partial t} = 0$ the Maxwell's equations are equivalent to wave equations

$$\begin{aligned} \nabla^2\phi - \frac{1}{c^2} \frac{\partial\phi}{\partial t} &= -\mu_0\mathbf{j} \\ \nabla^2\mathbf{A} - \frac{1}{c^2} \frac{\partial\mathbf{A}}{\partial t} &= -\rho/\epsilon_0 \end{aligned} \quad (\text{A.2})$$

The field of an electron moving with uniform velocity must be carried convectively along with the electron which implies that the time and space derivatives are not independent, i.e.

$$\frac{\partial}{\partial t} = -\mathbf{v} \cdot \nabla \quad (\text{A.3})$$

For example, if the electron moves along x direction, the wave equation becomes

$$\left(1 - \frac{v^2}{c^2}\right) \frac{\partial^2 \phi}{\partial x^2} + \frac{\partial^2 \phi}{\partial y^2} + \frac{\partial^2 \phi}{\partial z^2} = -\rho/\epsilon_0 \quad (\text{A.4})$$

Changing the variables to $\underline{x} = x/\sqrt{1 - v^2/c^2}$, $\underline{y} = y$, $\underline{z} = z$ we get the electrostatic Poisson equation

$$\underline{\nabla} \phi = -\rho(\sqrt{1 - v^2/c^2} \underline{x}, \underline{y}, \underline{z})/\epsilon_0 \quad (\text{A.5})$$

with the solution

$$\phi(\underline{x}, \underline{y}, \underline{z}) = \frac{1}{4\pi\epsilon_0} \int \frac{\rho(\underline{x}', \underline{y}', \underline{z}')}{\sqrt{(\underline{x} - \underline{x}')^2 + (\underline{y} - \underline{y}')^2 + (\underline{z} - \underline{z}')^2}} d\underline{v}' \quad (\text{A.6})$$

Changing back to the original variables the solution becomes

$$\phi(\underline{x}, \underline{y}, \underline{z}) = \frac{1}{4\pi\epsilon_0} \int \frac{\rho(\underline{x}', \underline{y}', \underline{z}')}{s} d\underline{v}' \quad (\text{A.7})$$

with

$$s = \sqrt{(x - x')^2 + (1 - v^2/c^2)[(y - y')^2 + (z - z')^2]} = r\sqrt{1 - v^2/c^2 \sin^2 \theta} \quad (\text{A.8})$$

The angle θ is defined in the figure A.1. In particular for an electron with velocity $\mathbf{v}$,

$$\begin{aligned} \phi &= \frac{e}{4\pi\epsilon_0 s} \\ \mathbf{A} &= \frac{e\mathbf{v}}{4\pi\epsilon_0 c^2 s} \end{aligned} \quad (\text{A.9})$$

These are also called Liénard-Wiechert potentials, derived here for uniform motion, although in the general case the velocity can vary in time. Now we are in a position

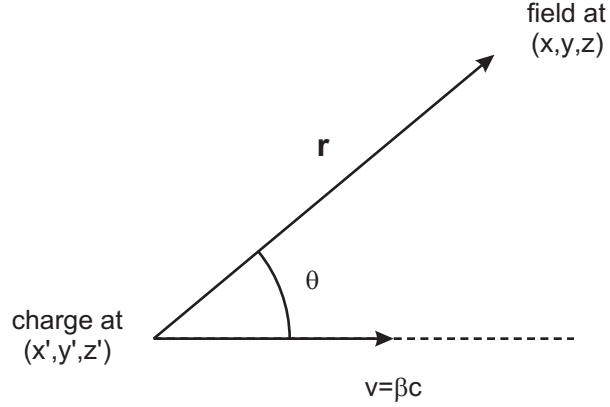


Figure A.1: The angle θ in the text is defined as the the angle between the velocity direction and the distance vector pointing from the charge location to the location of the electromagnetic fields.

to calculate the Lorentz force

$$\begin{aligned} \mathbf{F} &= \frac{e^2}{4\pi\epsilon_0} \left[-\nabla \left(\frac{1}{s} \right) + (\mathbf{v} \cdot \nabla) \frac{\mathbf{v}}{c^2 s} + \frac{\mathbf{v}}{c^2} \times \left(\nabla \times \frac{\mathbf{v}}{s} \right) \right] \\ &= -\frac{e^2}{4\pi\epsilon_0} \nabla \left(\frac{1 - v^2/c^2}{s} \right) \end{aligned} \quad (\text{A.10})$$

The result is that the force can be expressed as gradient of a potential, called the convective potential.

$$\mathbf{F} = -\nabla\psi, \quad \text{where} \quad \psi = \frac{e^2(1 - v^2/c^2)}{4\pi\epsilon_0 s} \quad (\text{A.11})$$

The scalar convective potential does not have spherical symmetry about the electron, see how s is defined in A.8.

The electric field of a moving electron, using A.9 in A.1 is

$$\mathbf{E} = \frac{e\mathbf{r}(1 - v^2/c^2)}{4\pi\epsilon_0 s^3} = \frac{e\mathbf{r}}{4\pi\epsilon_0 r^3} \frac{1 - v^2/c^2}{(1 - v^2/c^2 \sin^2 \theta)^{3/2}} \quad (\text{A.12})$$

A.2 Charge in arbitrary motion

A general solution for A.2 for a charge in arbitrary motion, not just uniform motion is

$$\begin{aligned}\phi(x, y, z, t) &= \frac{1}{4\pi\epsilon_0} \int \frac{[\rho(x', y', z')]}{R} dv' \\ \mathbf{A}(x, y, z, t) &= \frac{\mu_0}{4\pi} \int \frac{[\mathbf{j}(x', y', z')]}{R} dv' \\ R &= \sqrt{(x - x')^2 + (y - y')^2 + (z - z')^2}\end{aligned}\tag{A.13}$$

where square brackets are evaluated at a retarded time $t' = t - R/c$. These are known as *retarded potentials* and they can be visualized as follows [?]. Consider an observer situated at the point r , see figure A.2, and let a sphere centered at r contract with radial velocity c such that it converges on the point at the time of observation t . The time at which this information-collecting sphere passes the source at point r' is then the time at which the source produced the effect which is felt at r at time t .

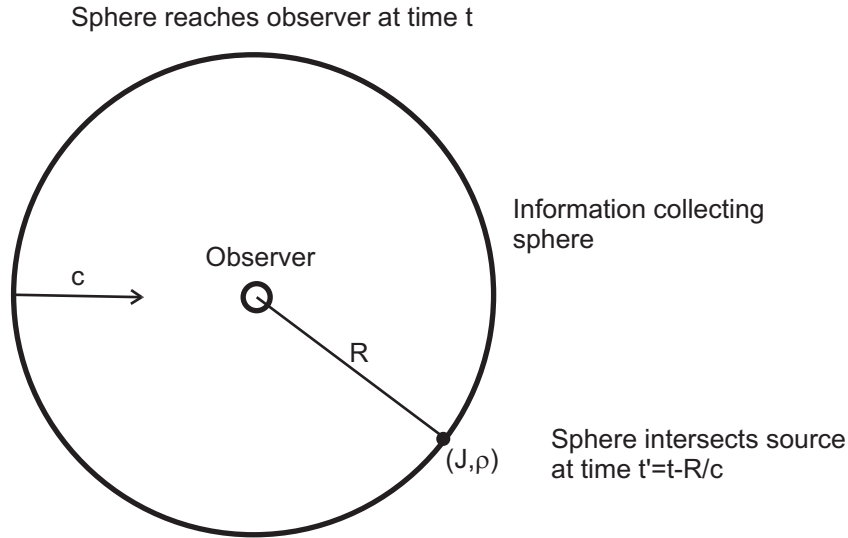


Figure A.2: A helpful instrument in keeping track of the time is to imagine a sphere collecting information for retarded potentials. As the sphere moves towards the observer with the speed of light, it carries information about the field at the observer that is generated by the charges that intersect the sphere.

Care must be taken when applying the concept of retarded potential because the integrand $[\rho(\mathbf{r}')d\mathbf{r}']$ is evaluated at different times. As the information collecting sphere sweeps over the charge distribution, the charges may move so as to appear more or less dense. If the charges move in the same direction as the converging sphere the volume integral of the *retarded charge* density will be more than the total charge and if charges move in opposite direction the integral will give less than the total charge. The retarded potential of an approaching charge will be greater than that of a receding charge at the same distance from an observer, since the approaching charge stays longer within the information collecting sphere.

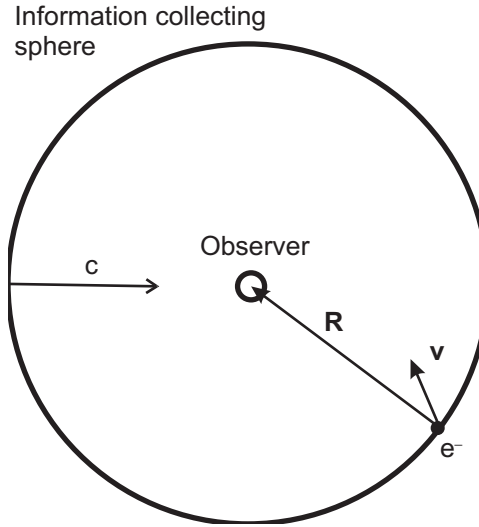


Figure A.3: The information collecting sphere and a moving electron.

In the case of an electron approximated as a point charge, we can express the total charge in terms of the retarded charge in the following way, see figure A.3:

$$e = [e] - [e] \frac{\mathbf{v} \cdot \mathbf{R}}{c} \quad (\text{A.14})$$

where $\mathbf{v}$ is the speed of electrons. The retarded potentials are then

$$\phi(\mathbf{r}, t) = \frac{1}{4\pi\epsilon_0} \frac{e}{[R - \mathbf{v} \cdot \mathbf{R}/c]} \quad (\text{A.15})$$

$$\mathbf{A}(\mathbf{r}, t) = \frac{\mu_0}{4\pi} \frac{e\mathbf{v}}{[R - \mathbf{v} \cdot \mathbf{R}/c]}$$

also called Liénard-Wiechert potentials for an electron (the square brackets are evaluated at $t' = t - R/c$).

For an electron in uniform motion one can show with the help of figure A.4 that the quantity $[R - \mathbf{v} \cdot \mathbf{R}/c]$ in the denominator is exactly s in A.8 (see [?]).

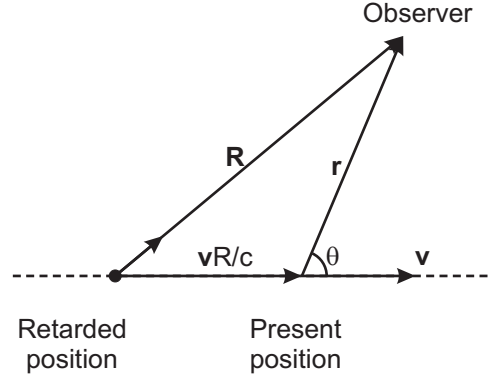


Figure A.4: Retarded and present position of a moving charge.

From the figure, with the help of the relations $\mathbf{r} = \mathbf{R} - \mathbf{v}R/c$ and $\mathbf{r} \times \mathbf{v} = \mathbf{R} \times \mathbf{v}$, we get

$$\begin{aligned} (R - \mathbf{v} \cdot \mathbf{R}/c)^2 &= r^2 - \left(\frac{\mathbf{r} \times \mathbf{v}}{c} \right)^2 \\ &= r \sqrt{1 - \frac{v^2}{c^2} \sin^2 \theta} \\ &= s^2 \end{aligned} \quad (\text{A.16})$$

Appendix B

Labview code for the sample manipulator

As the manipulator has to be quite versatile and is used for many different procedures, the software written in Labview 6.1 was structured as a state machine, similar to how a computer works. A state machine can be in any of a collection of states. At every step the machine evaluates its input and decides what state it will be in the next step. A schematic of the code implementing the state machine is given in figure below. The hierarchy of the code and one of the monitoring front panel are shown next.

All the Labview components of the file send text commands to a controller for the stepper motors that move the manipulator.

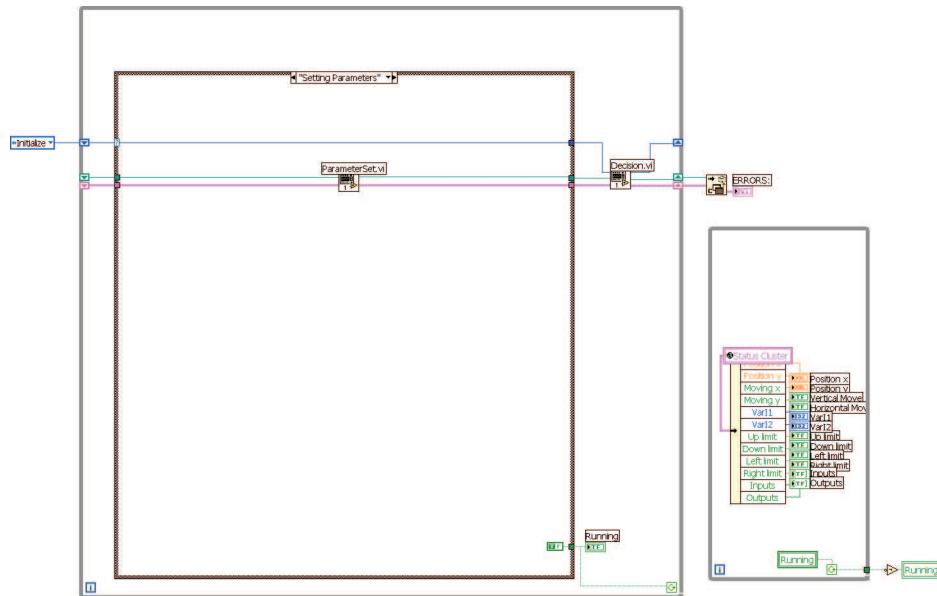


Figure B.1: Labview diagram implementing the manipulator control as a state machine. The states are shown pasted inside the *Case* structure. One can see the monitoring cluster on the right. The two *While* structures run in parallel, both being terminated by the variable *Running*.

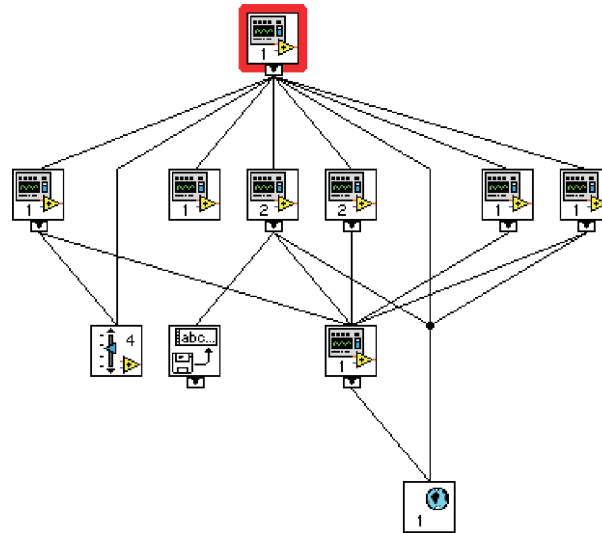


Figure B.2: Labview hierarchy of the program that controls the manipulator. The program spends most of its time in one of the states on the second level. *UpdateStatus* displays the information contained in the *GlobalStatus* variable. The list of exposure is read from a file in *HitPlan*.

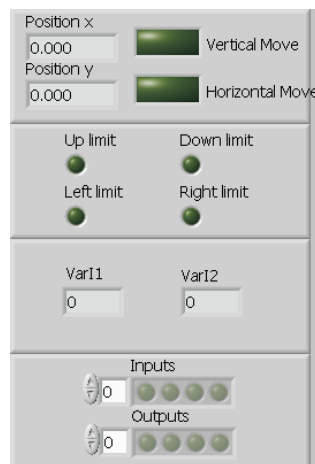


Figure B.3: Labview monitoring front panel. Var11 and Var12 are used for monitoring multiple shots. The lower inputs and outputs can be used for different triggers

Appendix C

Comparison: Electron Bunch and Half Cycle Pulses

A gaussian shaped electron bunch has an associated EM field that travels along with it with the same gaussian shape. To a stationary observer, this field very much resembles to a half cycle of an oscillating electromagnetic field. However, this is not a radiation field as it doesn't travel to infinity but is localized around the electron bunch.

There is a method to generate a true radiation field that also resembles a half cycle most of the time. By illuminating a wafer of biased GaAs semiconductor with a short pulse of laser light electrons are promoted to the conduction band. While in the insulating band, each GaAs wafer can hold off several kilovolts across 1 *cm* without breaking down.

A schematic of the half cycle pulse (HCP) production process [?] is shown in figure C.1. When the laser pulse hits the wafer, electrons within the wafer quickly accelerate due to the bias field. The accelerating electrons radiate a short pulsed field which propagates away from the wafer. The radiated field is polarized along the bias axis, its amplitude is proportional to the amplitude of the bias field and its rise time is

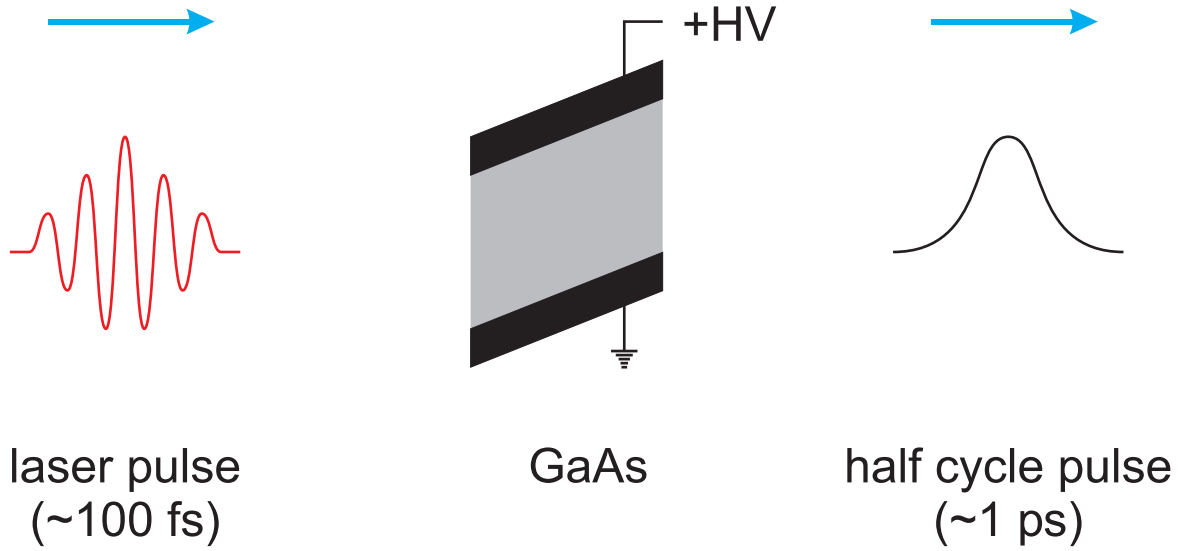


Figure C.1: Schematic showing the method to produce half cycle pulses of radiation field. A large amount of conduction electrons are produced in a short time by the laser pulse. These electrons are accelerated in the high voltage (+HV) bias and radiate. The radiated field shape follows the shape of the acceleration curve.

about 0.5 *ps*. The HCP field produced by the GaAs wafer scales linearly with the area of the wafer up to an area of approximately 1 *cm*².

The wafer returns to insulating state after the laser pulse has past, but this transition is much slower and electrons decelerate over a period of hundreds of picoseconds [?]. The deceleration produces a field in the opposite direction to that of the initial field, however the maximum strength of the "recoil" field is typically a factor of 5 – 10 smaller than the initial pulse height. A graphical representation of a typical HCP temporal profile is shown in figure C.2.

Although the pulse is called "half cycle" it has a negative part that is about 100 times longer in duration and lower in amplitude. This can be seen clearly by comparing the Fourier transform of a half sine cycle C.1, C.3 with that of a full cycle having the negative part stretched C.2, C.4.

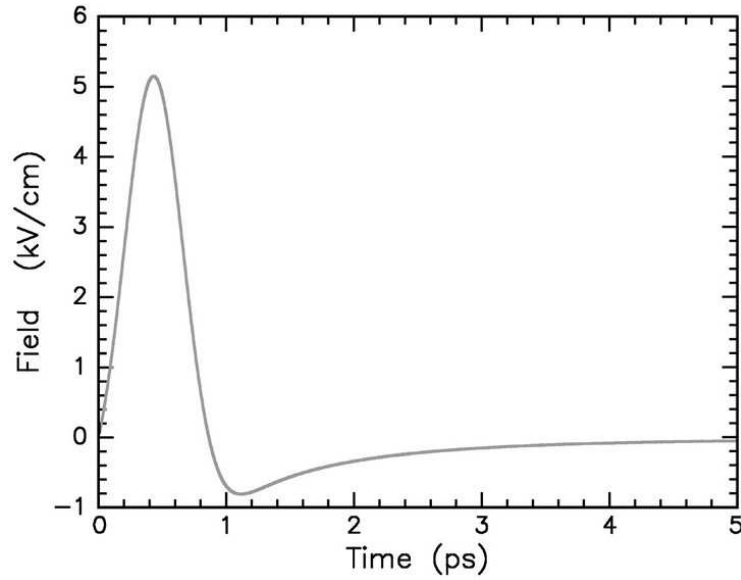


Figure C.2: The shape of the electric field from a typical half cycle pulse. The initial positive pulse is about 1 *ps* in duration and the negative tail persists for hundreds of picoseconds [?].

$$\mathbf{E}(t) = \begin{cases} \mathbf{E}_0 \sin(\omega t) & -\pi/2 < \omega t < 0, \\ 0 & \text{elsewhere} \end{cases} \quad (\text{C.1})$$

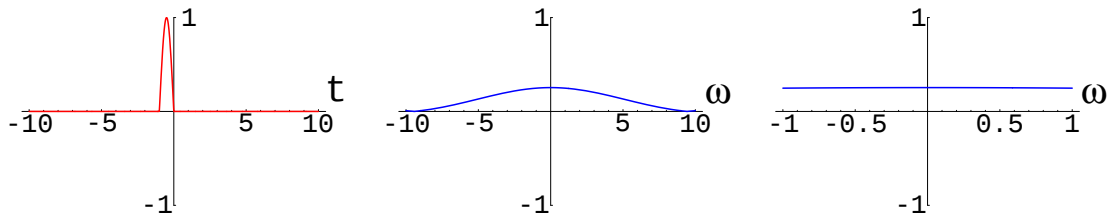


Figure C.3: The Fourier transform of a half cycle of a sine wave with a zoom in around zero frequency. There is a zero frequency component proportional to the area under the pulse.

$$\mathbf{E}(t) = \begin{cases} \mathbf{E}_0 \sin(\omega t) & -\pi/2 < \omega t < 0, \\ \mathbf{E}_0/a \sin(\omega t/a) & 0 < \omega t < \pi/2, a \in \{1, 10, 100\}, \\ 0 & \text{elsewhere} \end{cases} \quad (\text{C.2})$$

The pure half cycle has a zero frequency component whereas the stretched full cycle doesn't have it. This zero frequency component is directly proportional to the total integral of the electric field. Fourier-transform detection of HCP has been done, see C.5, and its spectrum has a shape similar to the full cycle with the negative part stretched [?].

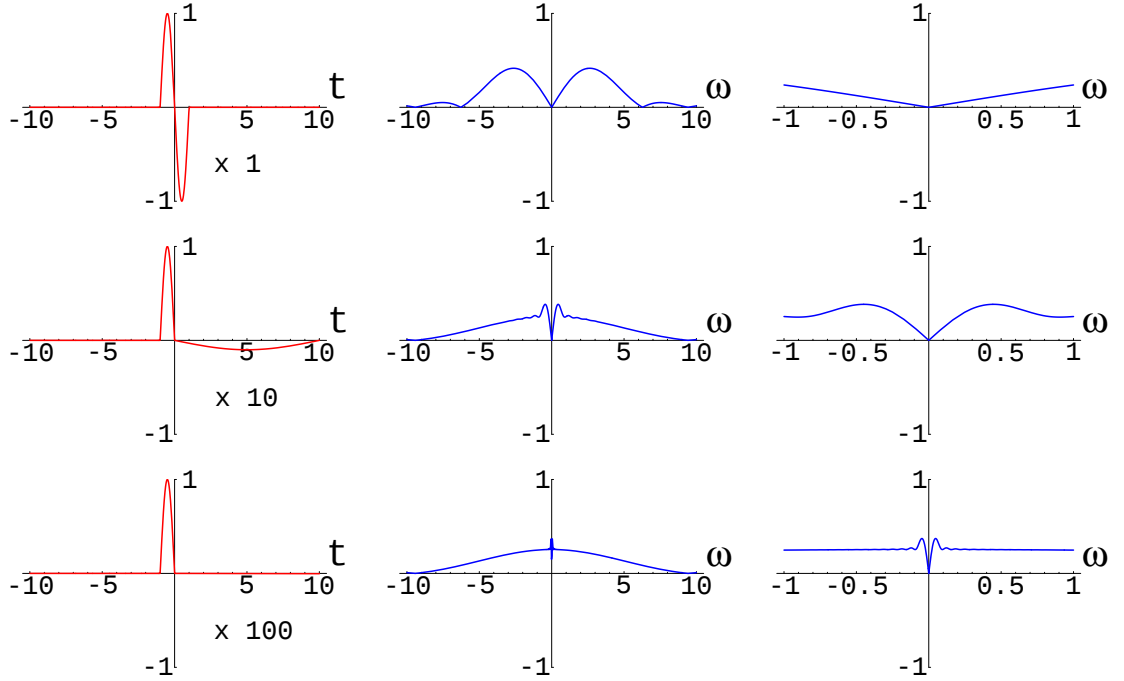


Figure C.4: The Fourier transform of a full cycle of a sine wave having the negative part stretched, with a zoom in around zero frequency. There is no zero frequency component.

The direction of the THz radiation can actually be controlled by the incident laser as shown in the picture C.6. The angles are given by the nonlinear Snell law, with

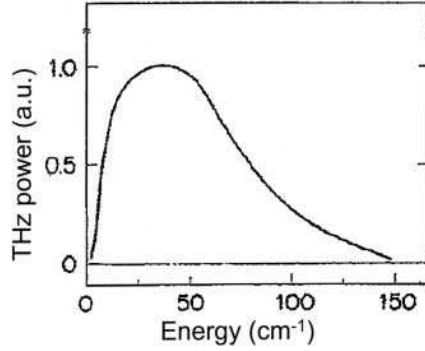


Figure C.5: Spectrum of a half cycle pulse determined by Fourier-transform detection [?]. Compare it with figure C.4.

frequency dependent refraction index. Because of the tilt of the laser beam there is a phase delay in the radiation from different parts of the emitter that in the end make the radiation concentrate along the angle given by the Snell Law. The generation of THz radiation can also be thought as a nonlinear effect where the mixing of different frequencies in the incoming beam gives the THz radiation as a difference.

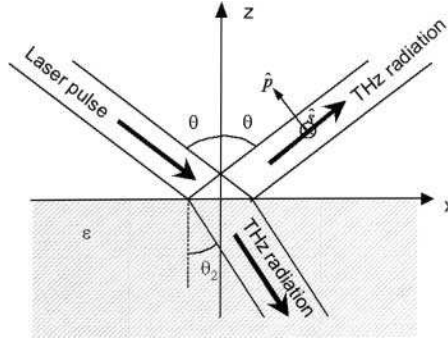


Figure C.6: Direction of a half cycle pulse is determined by Snell's law [?].

The acceleration of the charge carriers in the electric bias field is the most critical aspect of THz because this is the process that determines the temporal evolution of the radiated electric field. It can be viewed as involving an initial ballistic acceleration of the carriers on a time scale shorter than the carrier scattering time, followed by an approach to drift velocity. For high enough density of charge carriers the initial acceleration can lead to a space charge that can screen the bias field reducing the

efficiency of the THz generation. A simulation for the dynamics of the charge in an emitter biased perpendicular to the surface by doping is shown in figure C.7.

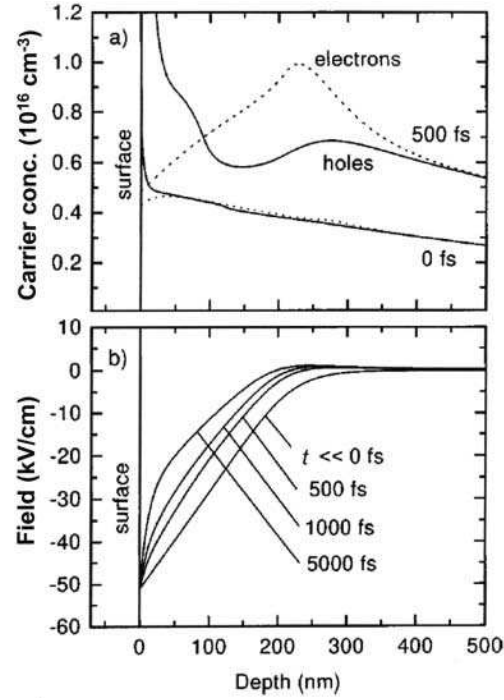


Figure C.7: Charge dynamics in an emitter biased by a surface depletion field. The changes in the field over time is due to space charge screening [?].

Appendix D

Coherent Magnetic Switching via Magnetoelastic Coupling

D.1 Stress Induced, Dynamically Tunable Anisotropy

A magnetic moment is intrinsically linked to an angular momentum, either of the orbital or the spin type. I like to think of the magnetic storage as storage of information in little spinning things. To change a magnetic moment one has to supply angular momentum. The usual method is to use a magnetic field or, more recently, circularly polarized light that carries one quantum of angular momentum. Another way of angular momentum transfer is to use the coupling between spin and orbital angular momentum.

The magnetic moment in the ferromagnetic materials commonly used in information storage consists of mainly spin magnetic moment. The orbital magnetic moment is "quenched" by the crystal lattice, that is the electric interactions between the electron and the lattice prefers orbits that are equal combination of right and left circling electron. This quenching is not complete and there is a few percent orbital magnetic moment contribution to the total magnetic moment.

The important fact we care about here is that there is a very strong coupling of the orbital moment to the crystal lattice. There is also a weaker coupling of the orbital moment to the spin moment. As the electron moves about a charged atomic core it sees the moving core as an electric current which makes a magnetic field acting on its spin moment. An idea I have thought about is to coherently modify the crystal lattice, then the orbital moment, being strongly coupled to the lattice will very fast adjust its orientation to it after which the orbital moment will exert a torque on the spin moment via spin-orbit coupling.

There is a whole branch of magnetism that studies the coupling between the lattice and the magnetic moment, also called the magnetostriction. A correspondent phenomenon with electric field, the coupling between the crystal lattice and the electric dipole moment, is the electrostriction. Suppose we generate a mechanical stress in a piezoelectric material by applying an electric field to it, and adjacent to it we have a magnetic material in full mechanical contact. The stress transmitted to the magnetic material changes its crystal lattice and if this magnetic material has a large magnetoelastic coefficient it will change the orientation of the magnetic moment. What we have done in fact is generate angular momentum in the crystal lattice by applying an electric field, transfer it to the orbital angular momentum very fast and then transfer it more slowly to the spin moment via the spin-orbit coupling.

A simple magnetic device functioning as magnetic memory can be imagined using the above mechanism. A capacitor with electrodes made of strong metallic material, such as tungsten, has a dielectric made of good piezoelectric material. In between one of the electrodes and the piezoelectric we have a layer of magnetic material with high magnetoelastic coefficient. When we apply an electric voltage to the electrodes the piezoelectric contracts or expands in the fixed space provided by the mechanically strong electrodes. The stress is transmitted to the magnetic material and its magnetic moment will change its orientation. In principle one could use precessional switching

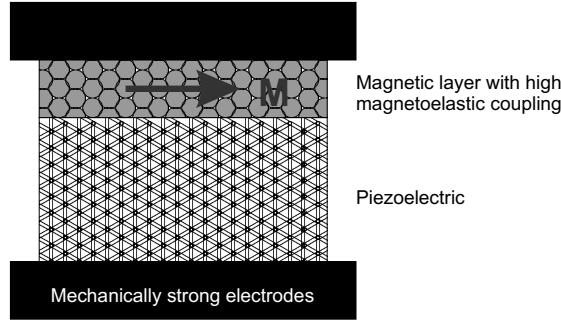


Figure D.1: An illustration of a memory device using the magnetoelastic effect. The piezoelectric layer converts the electric voltage into mechanic stress that changes the orientation of the magnetization M in the magnetic layer.

in the magnetic field generated by the mechanical stress; the precise timing could be provided by tuning the voltage pulse shape. With the simple ferromagnetic materials the magnetic field generated by stress can reach 1000 Oe . Thus the time scale of precessional switching is around 100 ps .

The induced anisotropy due to stress can be illustrated in the case of isotropic materials, i.e. with isotropic magnetoelastic coefficient. In this case the magnetoelastic energy has the form:

$$E_{mel} = \frac{3}{2} \lambda_s \sigma \sin^2 \theta = K_u \sin^2 \theta \quad (\text{D.1})$$

where λ_s is the magnetoelastic coefficient, σ is the stress, θ is the angle between the applied stress and the magnetization direction. $K_u = \frac{3}{2} \lambda_s \sigma$ is the uniaxial anisotropy energy density due to the stress; it can have both signs depending whether the stress is tensile ($\sigma > 0$) or compressive ($\sigma < 0$) [?]. For a positive magnetoelastic coefficient ($\lambda_s > 0$) a tensile stress will favor the alignment of magnetic moments with the direction of the stress. A compressive stress will favor the settling of the magnetic moments in a plane perpendicular to the stress direction, see figure . For a negative λ_s the behavior is opposite to the above.

The stress induced in a structure like the one in figure D.1 can be enhanced

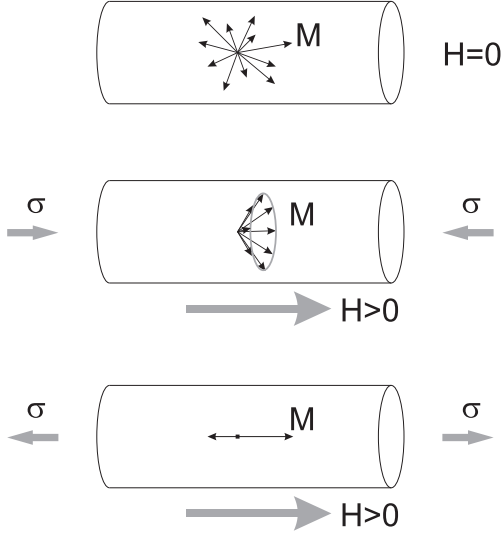


Figure D.2: The effect of stress anisotropy on the orientation of magnetization for a magnetic material with isotropic positive magnetostriction. With no magnetic field and no stress applied the magnetization has no preferred direction. A compressive stress will favor an orientation perpendicular to the stress direction and with an applied field the magnetization lies in a cone around the magnetic field direction. A tensile stress will tend to align the magnetization along its direction and an applied magnetic field will favor domains aligned with it.

when there is a resonance with the mechanical structure. The stress in the magnetic material can be several times the applied stress [?], the multiplication factor being the Q-factor of the mechanical resonator.

D.2 Spin Amplifier

An apparatus that uses the spin degree of freedom consists of polarizers, analyzers and spin rotators. The whole field of spin dependent electric conduction exploded with the use of the Giant Magneto-Resistance (GMR) effect in the read heads of magnetic hard drives. The system there consists of a polarizer and analyzer ferromagnetic layers with a non-magnetic metallic layer to transmit the spin polarized current. The stray magnetic field from the bits in the magnetic media changes the direction of the

polarizer and one can see this with the help of the analyzer layer.

Using the spin degree of freedom of conduction electrons means performing operation on their spin polarization (the normalized difference between the number of spin up and spin down electrons). Making an analogy with regular charge electronics, which took off after the invention of the transistor, one would need a spin transistor to build a spin polarization amplifier. A regular transistor is a current/voltage source which controlled by the input current/voltage. A spin transistor is a spin polarization source(a filter) controlled by the input spin polarization. One has to employ a spin dependent effect to build such a transistor.

An effect that is sensitive to the spin of the conduction electrons is the RKKY exchange interaction mediated by the conduction electrons. Localized magnetic moments are too far to have a direct exchange interaction but they polarize the mobile conduction electrons and through their polarization they interact with neighboring magnetic moments. Because the cutoff of the momenta near the Fermi surface the polarization of the conduction electron, in fact a spin screening effect, has an oscillatory behavior. The exchange coupling can be ferromagnetic or antiferromagnetic depending on the distance between neighboring magnetic moments [?], see figure D.3.

Imagine now a MOSFET type structure, see D.4, where the channel under the gate is an RKKY ferromagnetic material and we inject spin polarized electrons from the gate across the tunnel barrier. The exchange coupling constant in the channel depends on the polarization of the conduction electrons, so if we inject more we can shift the curve in figure D.3, for instance change the ferromagnetic coupling into an antiferromagnetic one. The channel will spin-filter the electrons that go through it when it is antiferromagnetic. This is now a spin-dependent spin source. There are weaknesses in this model however. For one thing we do not know if injecting polarized electrons does indeed affect the RKKY coupling, also once the coupling is

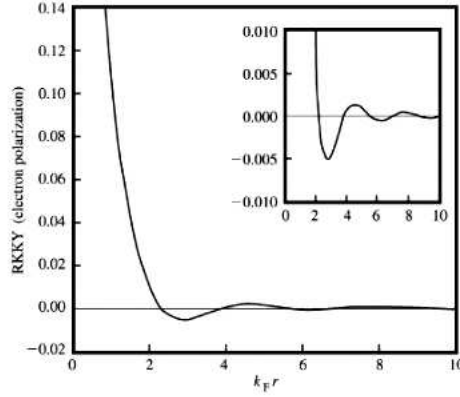


Figure D.3: RKKY coupling between two magnetic moments separated by a distance r , in three dimensions [?]. The figure can also be viewed as the negative of the electron spin polarization as a function of distance around a single magnetic moment. Positive value corresponds to ferromagnetic coupling, the distance is scaled by the Fermi wave vector and the inset shows the same plot with expanded vertical scale.

established maybe it will self-sustain itself and be hard to turn off. A ferromagnetic-antiferromagnetic phase transition will be sensitive to temperature and it may be slow.

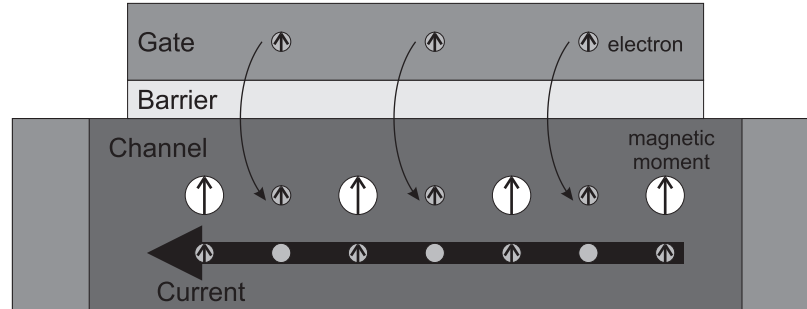


Figure D.4: A proposal for a spin transistor using the RKKY exchange coupling. polarized electrons are injected from the gate electrode across the barrier into the conducting channel. Here the injected electrons change the coupling between the magnetic moments. That in turn modifies the spin filter effect of the channel and the whole structure behaves like a spin-dependent spin filter, an important part of a spin amplifier.

A different idea for a spin amplifier comes up when one realizes that what matters

is actually the projection of the spin polarization on some direction. Thus, by rotating a polarizer (usually the magnetization of a ferromagnetic material) one can increase or decrease that projection, see figure D.5. The only thing remaining is to make this rotation dependent on the input spin polarization.

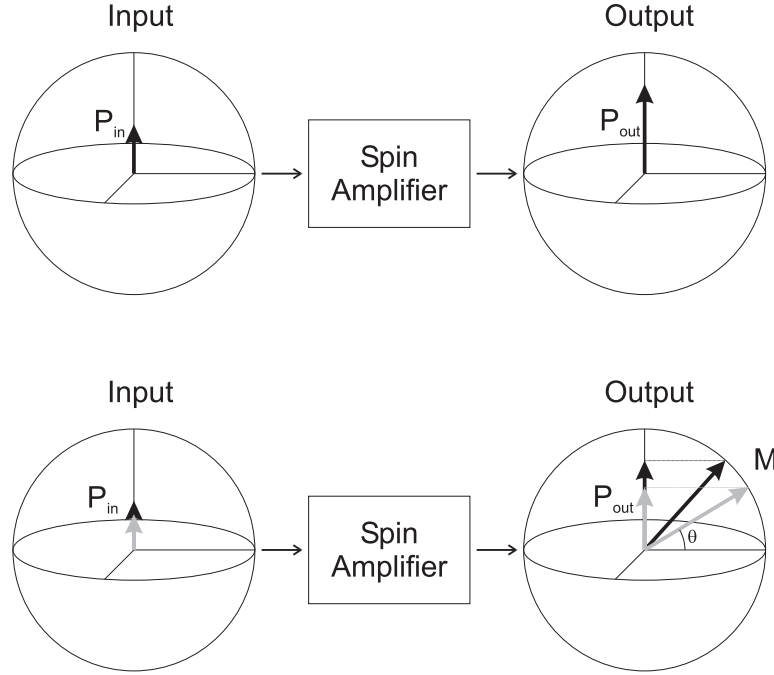


Figure D.5: A spin amplifier is supposed to increase the input spin polarization, shown here on the Poincaré sphere. It can do it either by increasing the length of the output polarization along the z-axis, as in the upper part of the picture, or it can rotate the unit polarization on the Poincaré sphere, thus changing the projection along z-axis, as in the lower part of the picture. The latter process is potentially easier to implement as the magnetization (spin filter) is easier to rotate than to increase.

A spin dependent rotation of the magnetization could be implemented in several ways. We now show an implementation using the magnetoelastic effect, see figure D.6. The orientation of the magnetization in D.1 is dependent on the stress that is given by the applied voltage. We can make the applied voltage spin dependent either by using a GMR structure or a TMR (tunnelling magneto-resistance) structure. The

TMR has a larger relative resistance change, it involves electrons tunnelling from one ferromagnetic layer to another across an insulating barrier, and is probably more suitable for sensing the input polarization in this case.

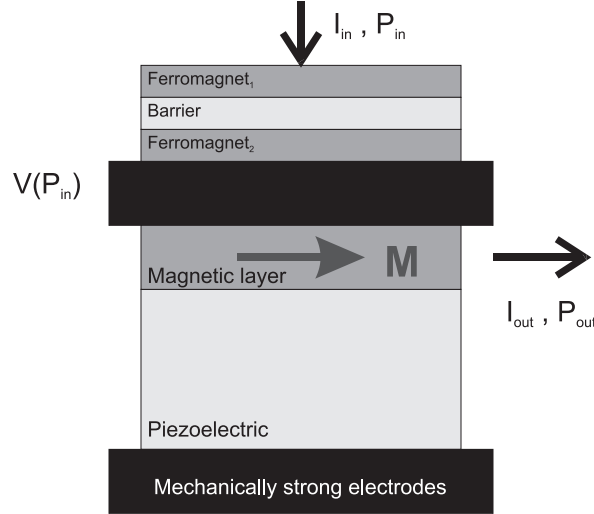


Figure D.6: A spin amplifier using the magnetoelastic effect and the tunnelling magnetoresistance (TMR). The TMR sensor converts the input spin polarization P_{in} into voltage V which in turn, through the piezoelectric layer, generates a mechanical stress that changes the orientation of the magnetization. The polarization P_{out} of the output current will depend on the input polarization.

The spin polarized devices can be implemented using semiconductor materials, in fact the spin decay length is hundreds of microns as compared to hundreds of nanometers in non-magnetic metals [?]. However, it is difficult so far to inject spin polarized electrons in semiconductors from metallic ferromagnetic layers because of conductivity mismatch and ferromagnetic semiconductors still have a long way to reach a room temperature Curie point. Nevertheless a spin transistor has been proposed, the Datta-Das transistor, see figure D.7. It is basically a MOSFET transistor with source and drain made of ferromagnetic material, acting as polarizer and analyzer. The gate creates an electric field in the channel and in some semiconductors the moving electrons see the electric field as a magnetic field in their frame of reference. This

magnetic field will make the spin of the electrons precess, this is the Rashba effect, in essence a spin-orbit coupling similar to the magnetoelastic coupling. We can make the electric field spin-dependent by placing a spin sensor on top of the gate, a GMR or TMR structure as above. This way we have a spin amplifier using semiconductors.

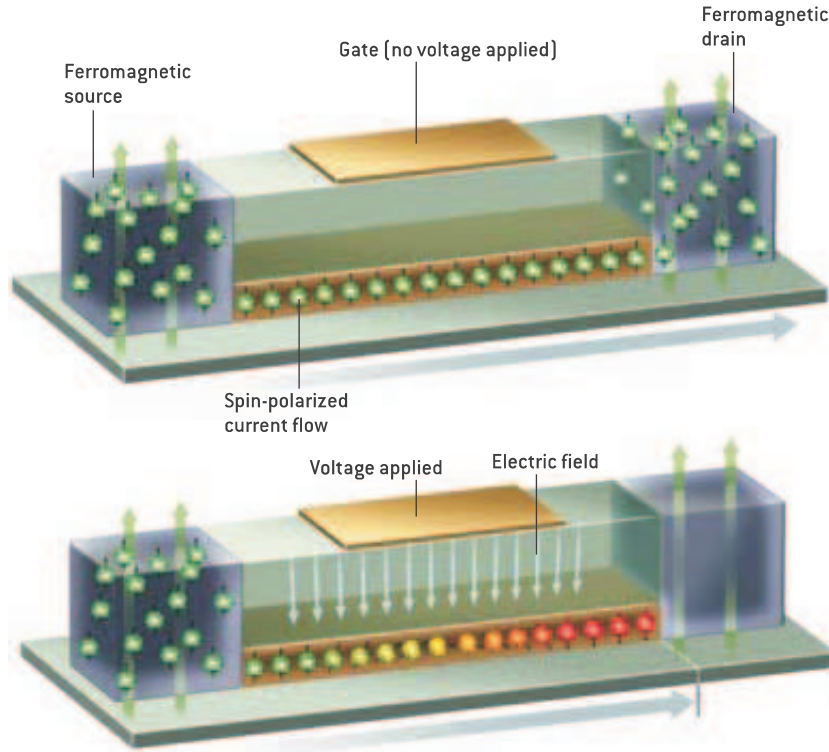


Figure D.7: The principle of Datta Das transistor. The electric field is transformed into a magnetic field in the frame of reference of the spin polarized electrons in the channel. This magnetic field rotates the spin polarization and one can have a variable resistance between the two ferromagnetic layers that act as polarizer and analyzer [?].